

Magneto-transport of electrons in near surface InAs quantum wells in contact with NbTiN

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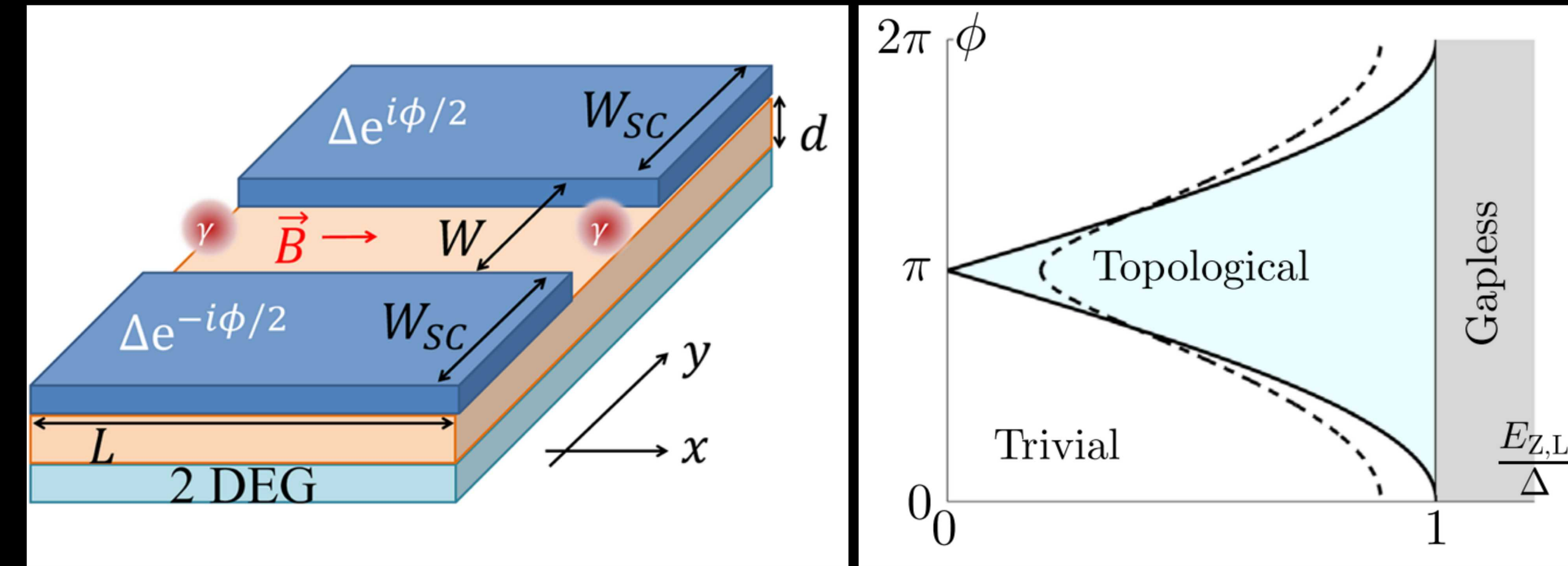
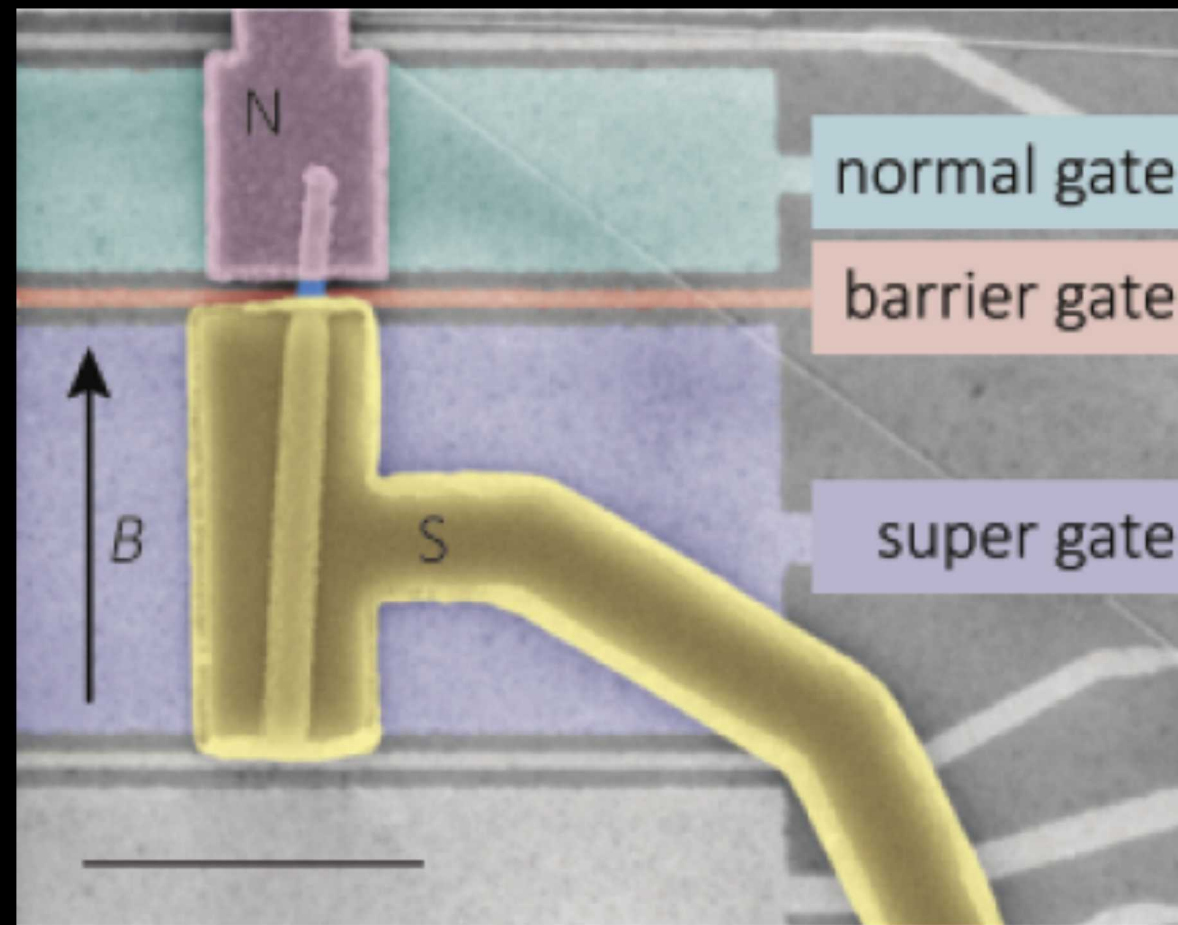
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Website: <https://wp.nyu.edu/shabanilab/>



Majorana fermions 1D vs 2D

- Strong motivation toward universal topological quantum computation.



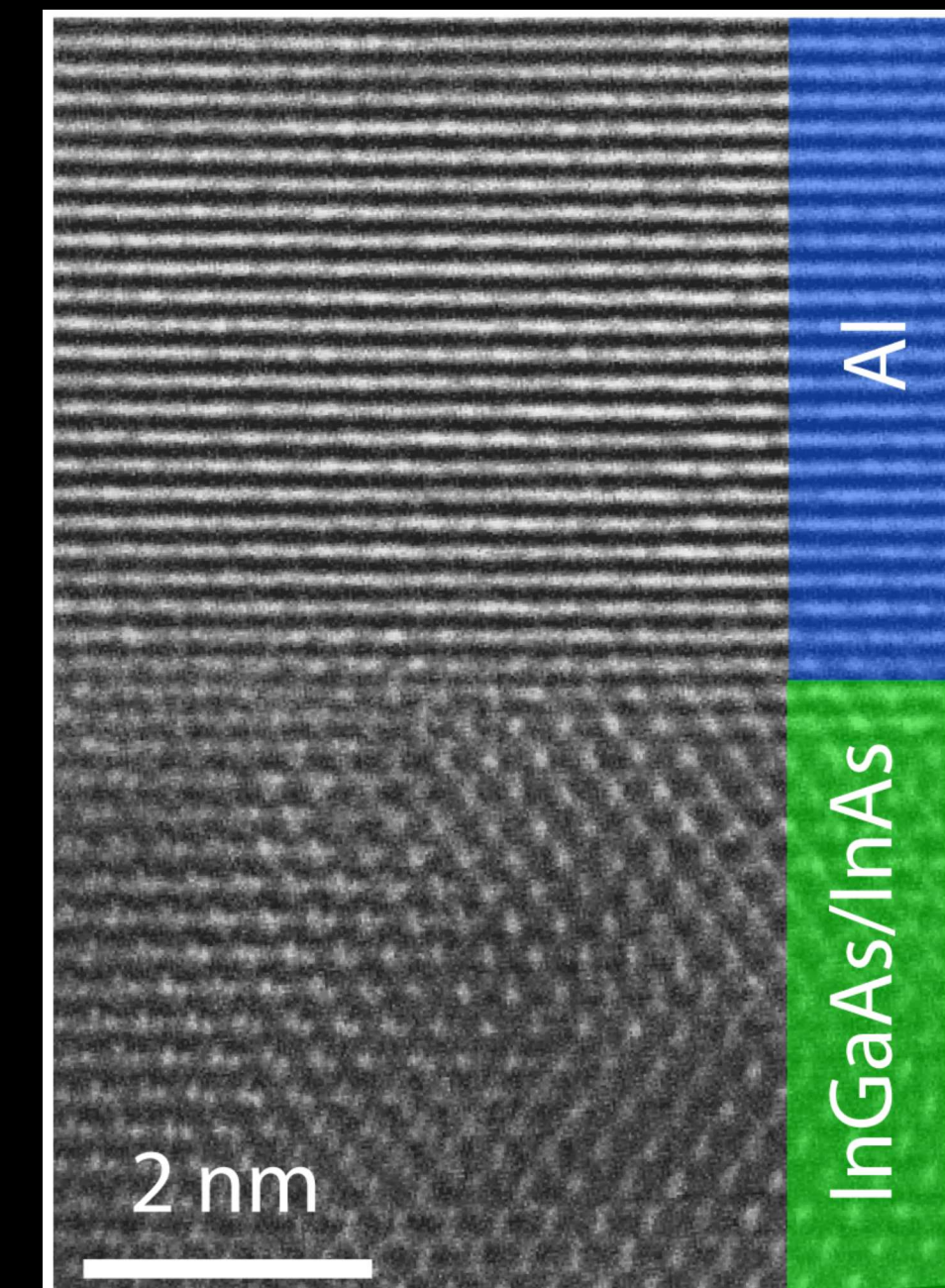
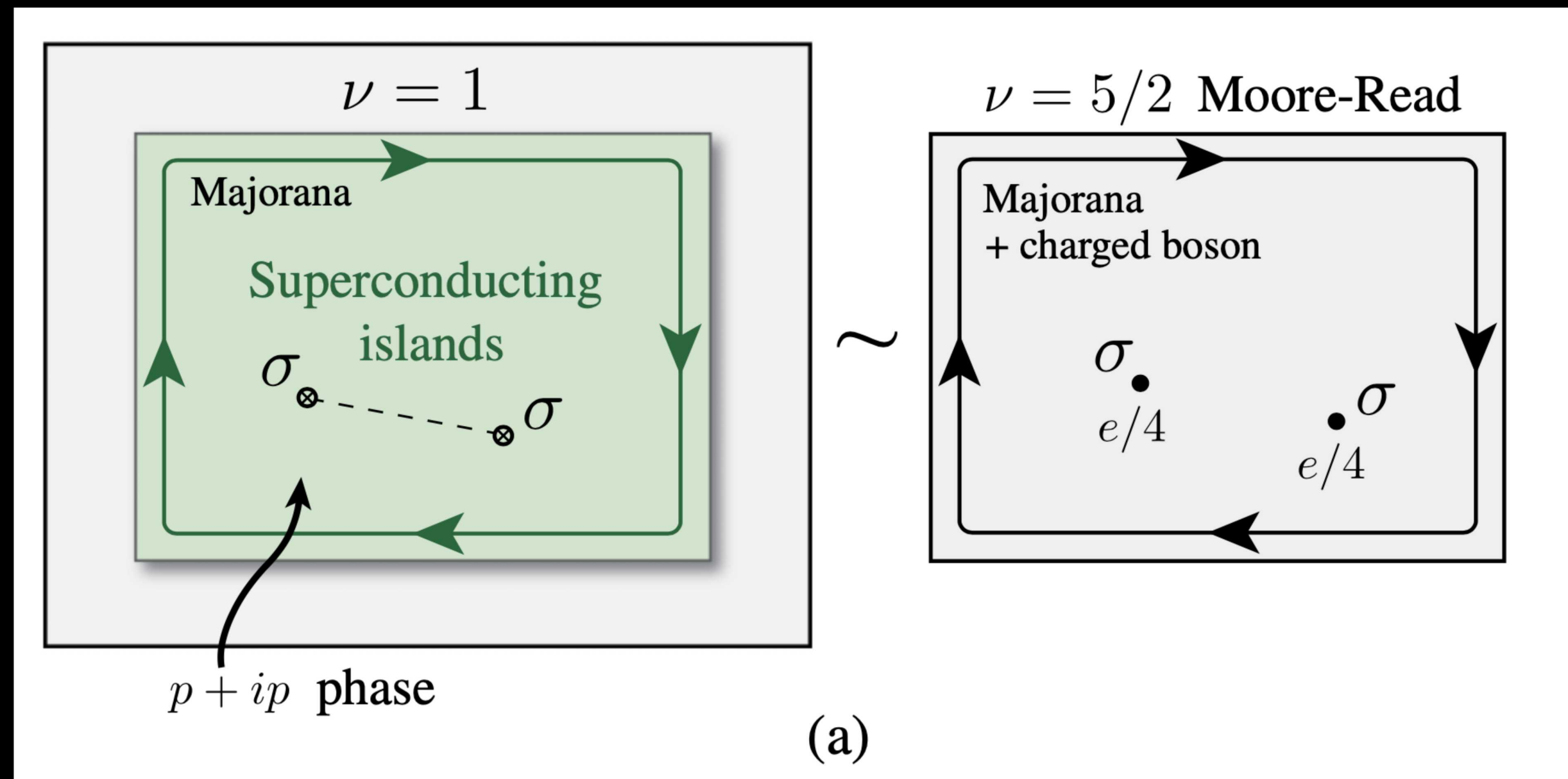
❑ 1D platform: bottom-up approach

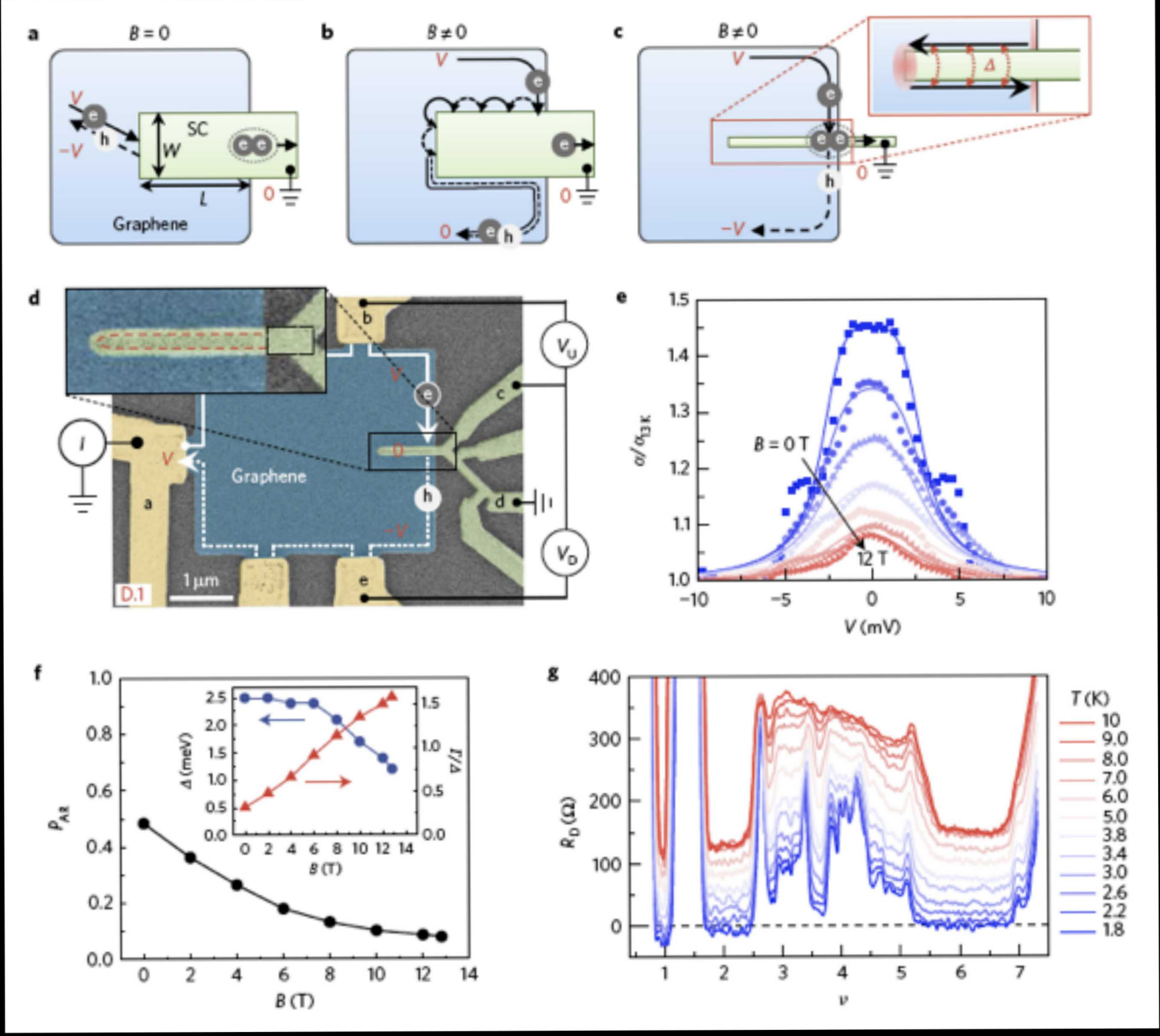
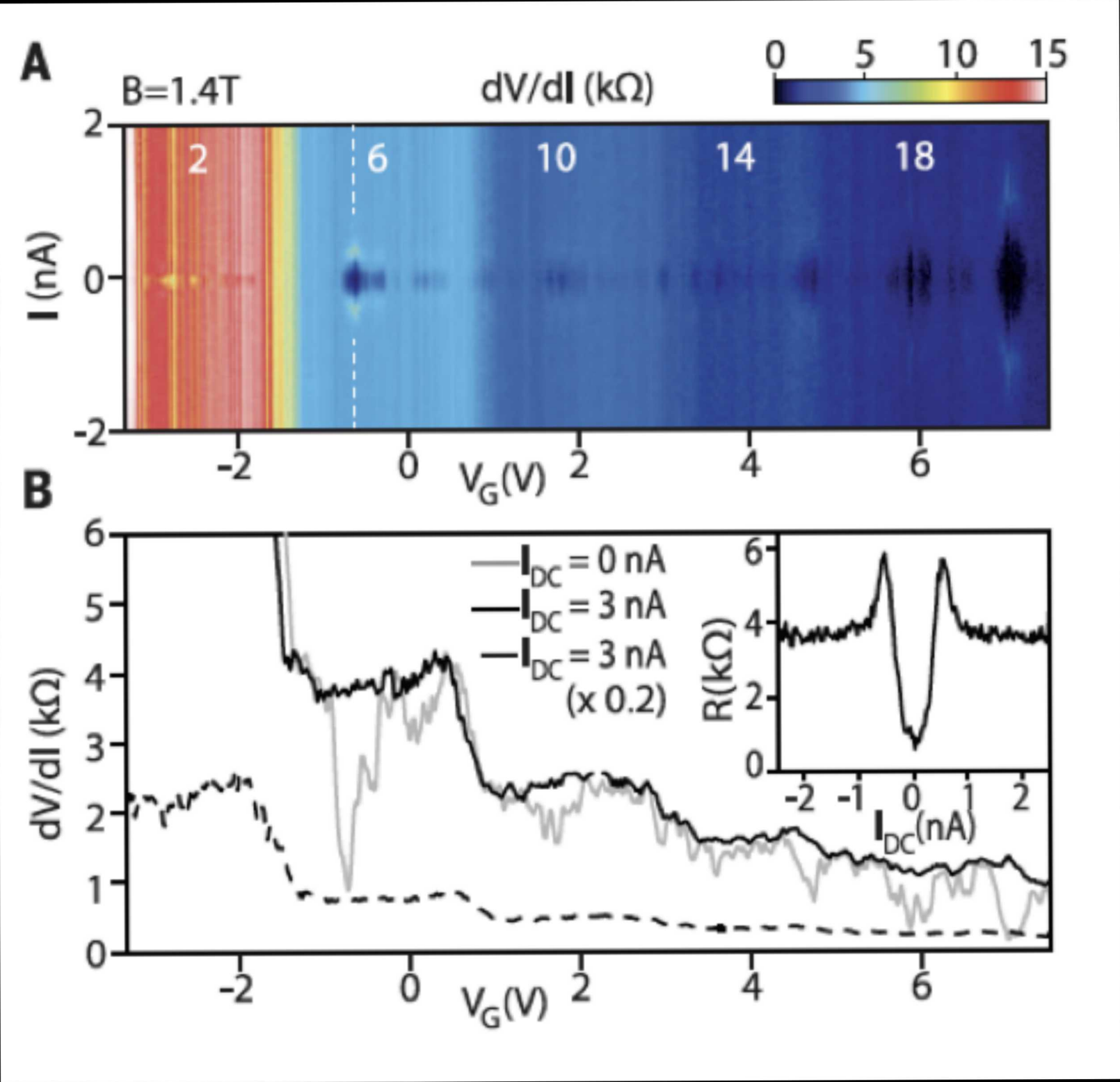
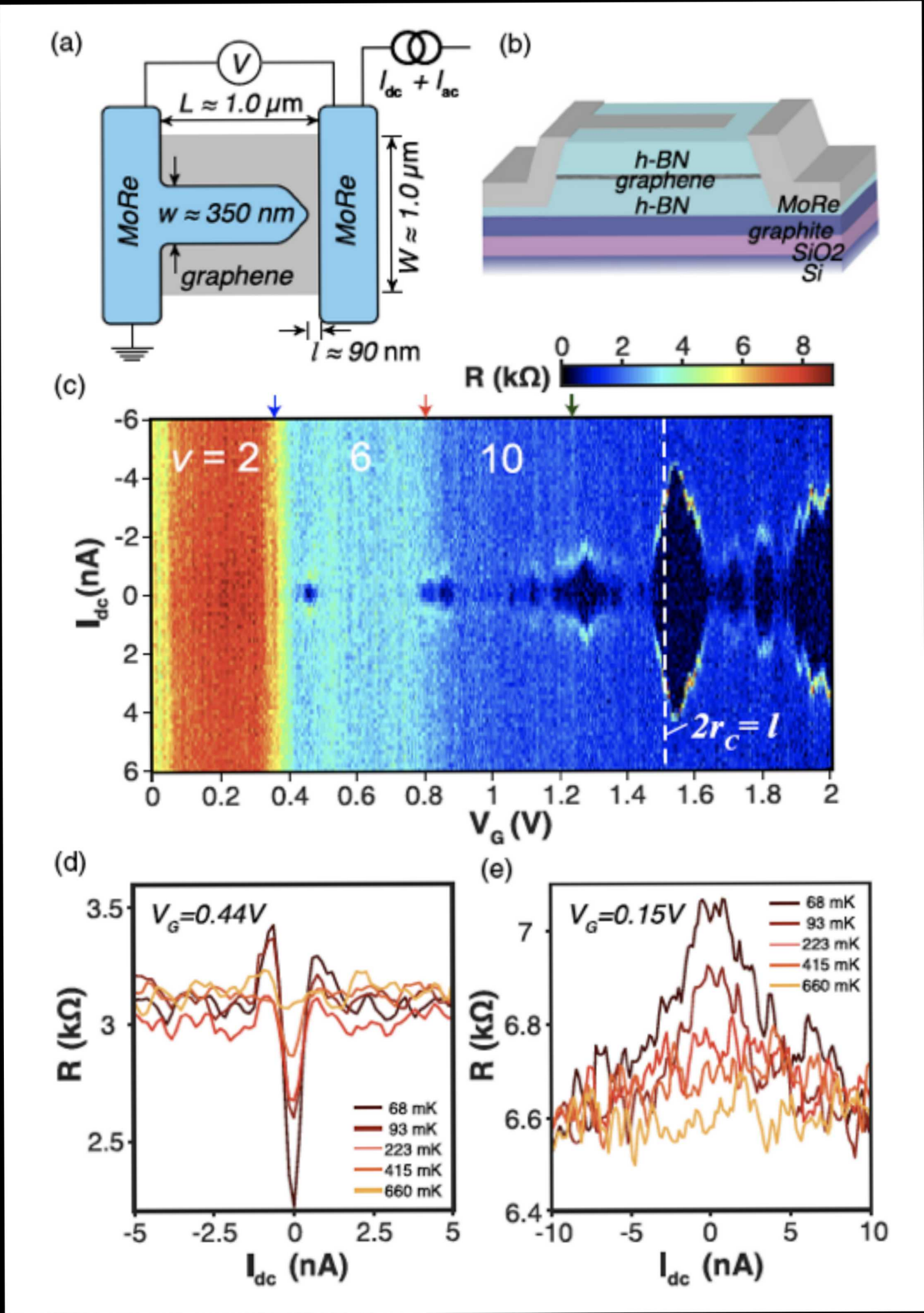
❑ Simple theory works well;

❑ 2D platform: top-down approach

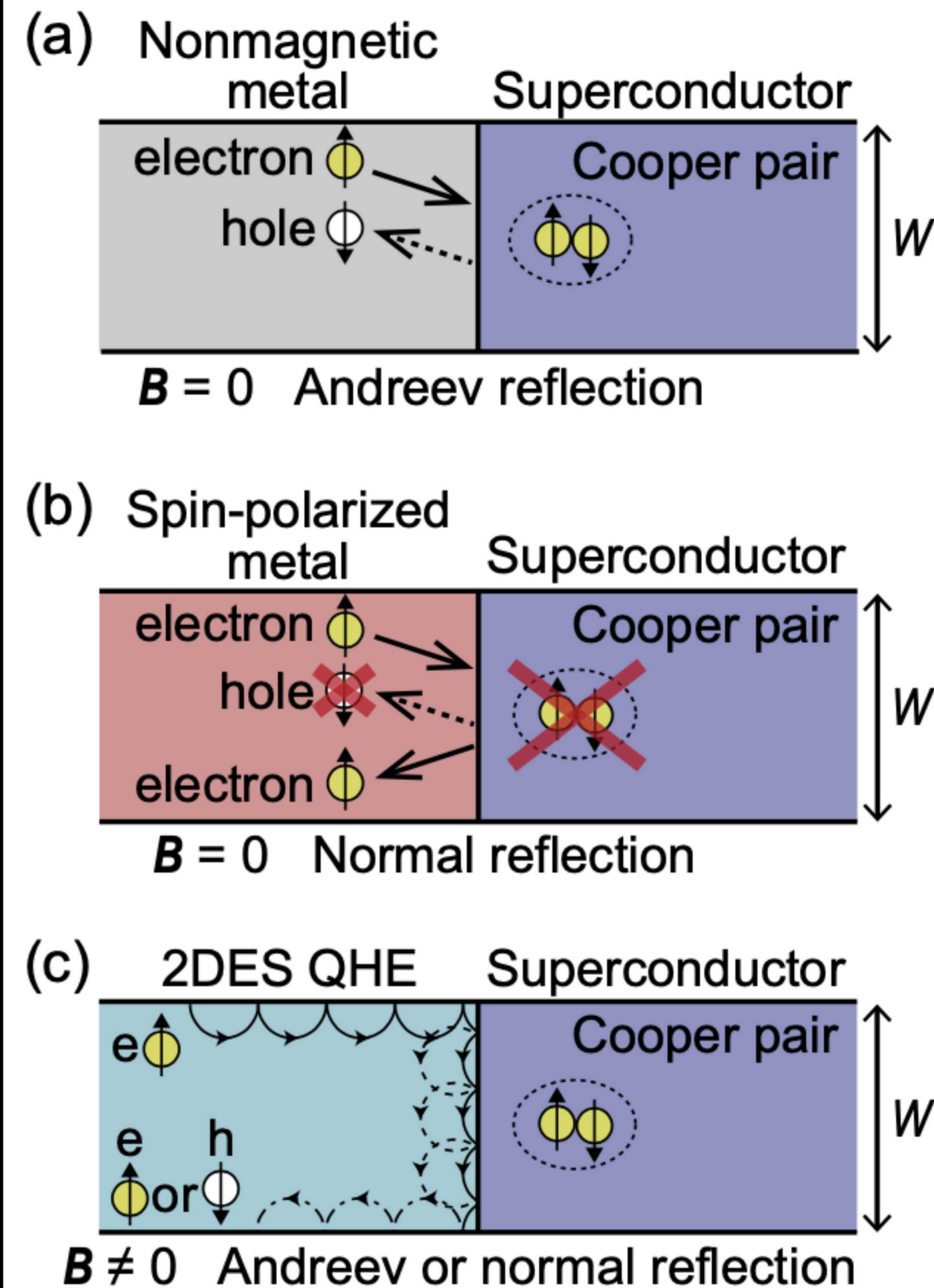
❑ Simulations are needed.

- Surface InAs quantum wells are promising material for topological superconductivity (e.g. Majorana fermions).



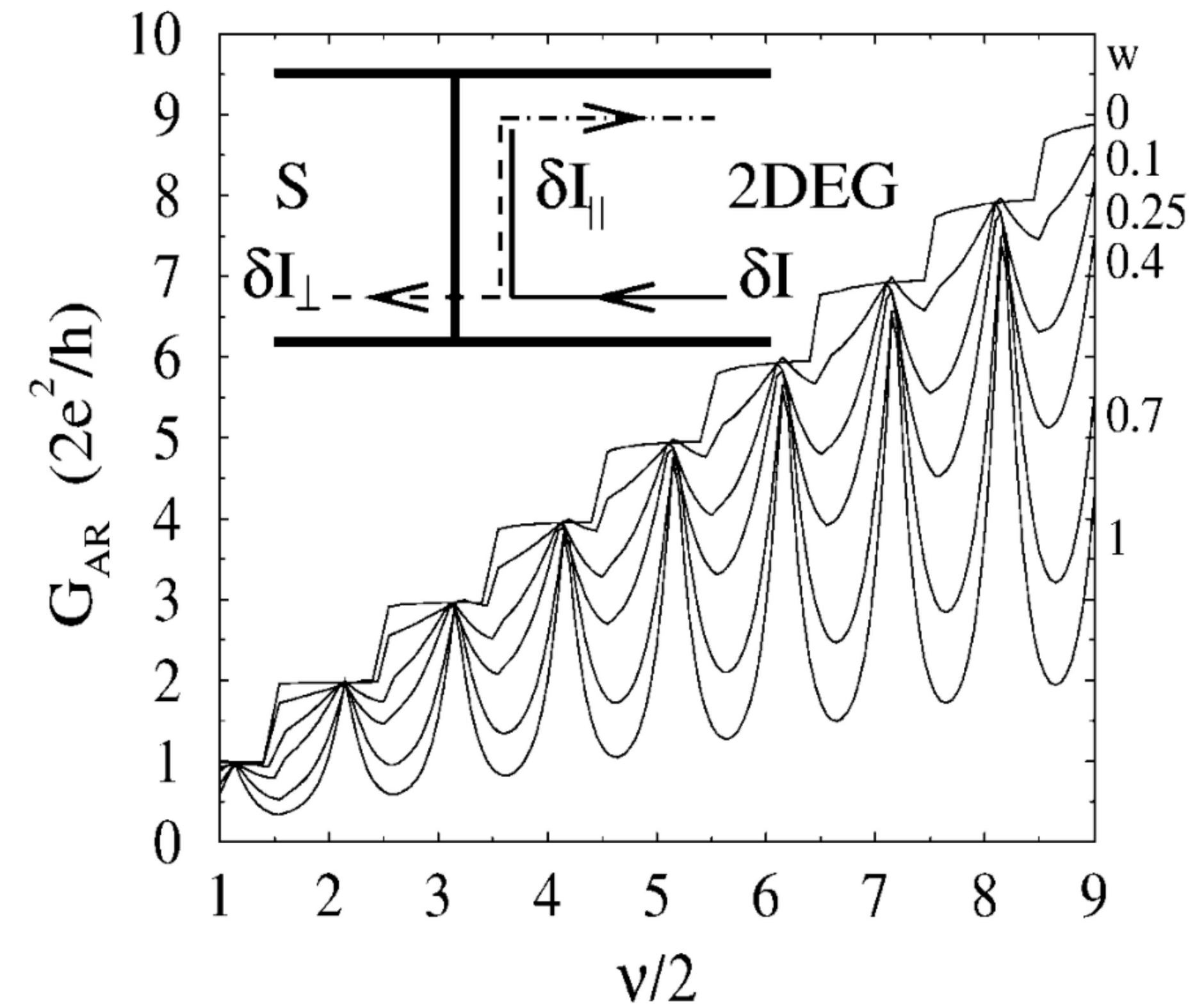


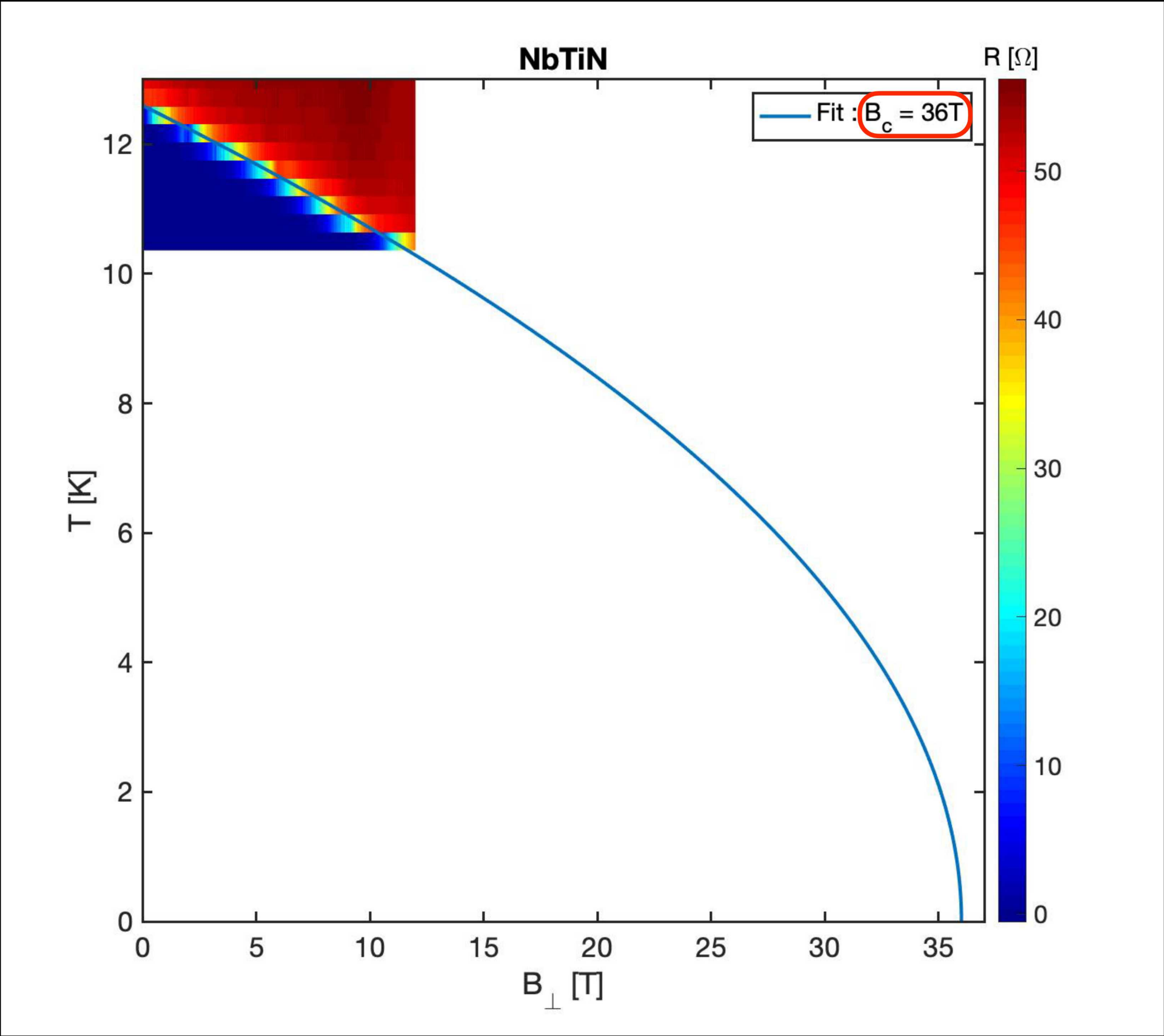
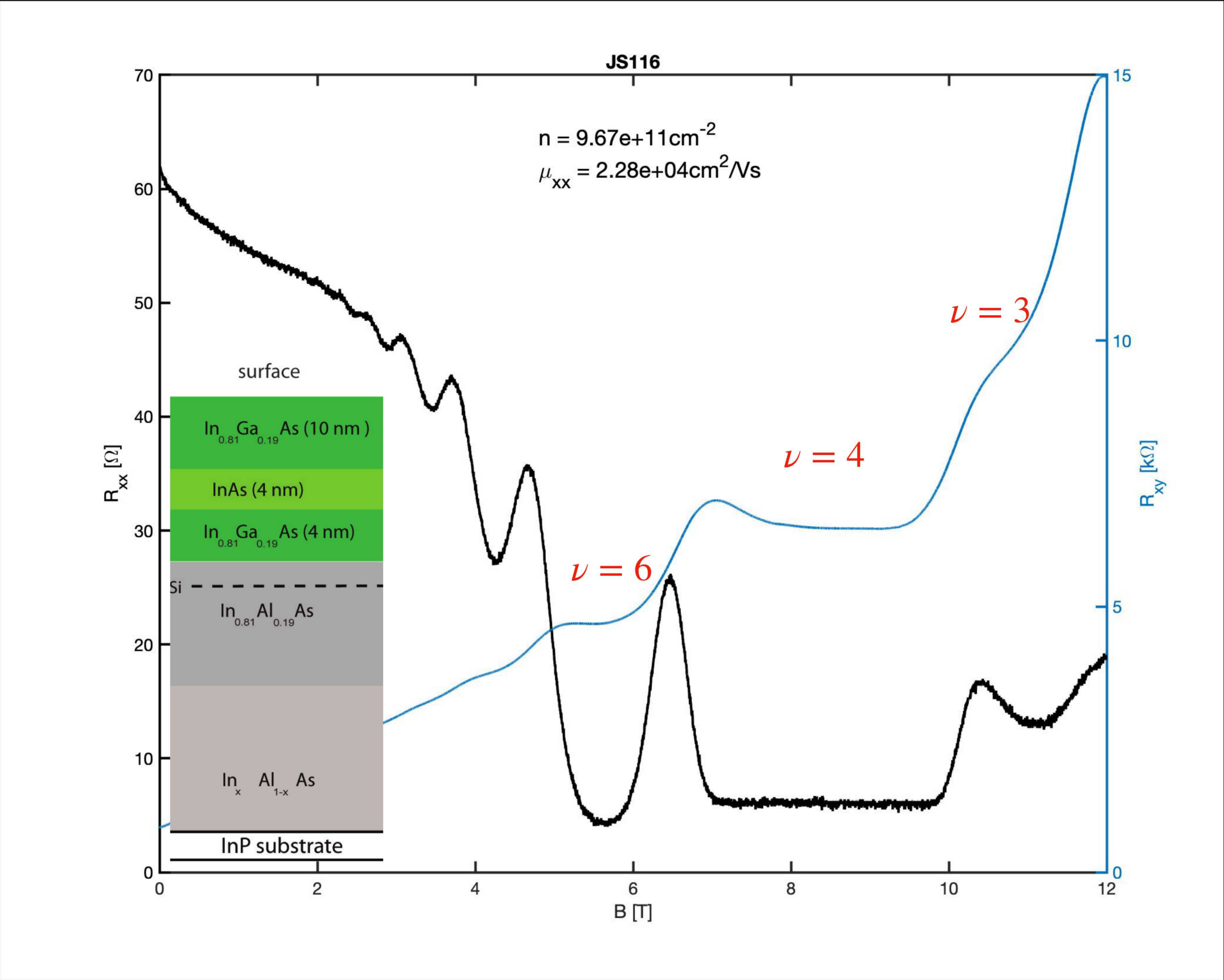
Andreev Reflection



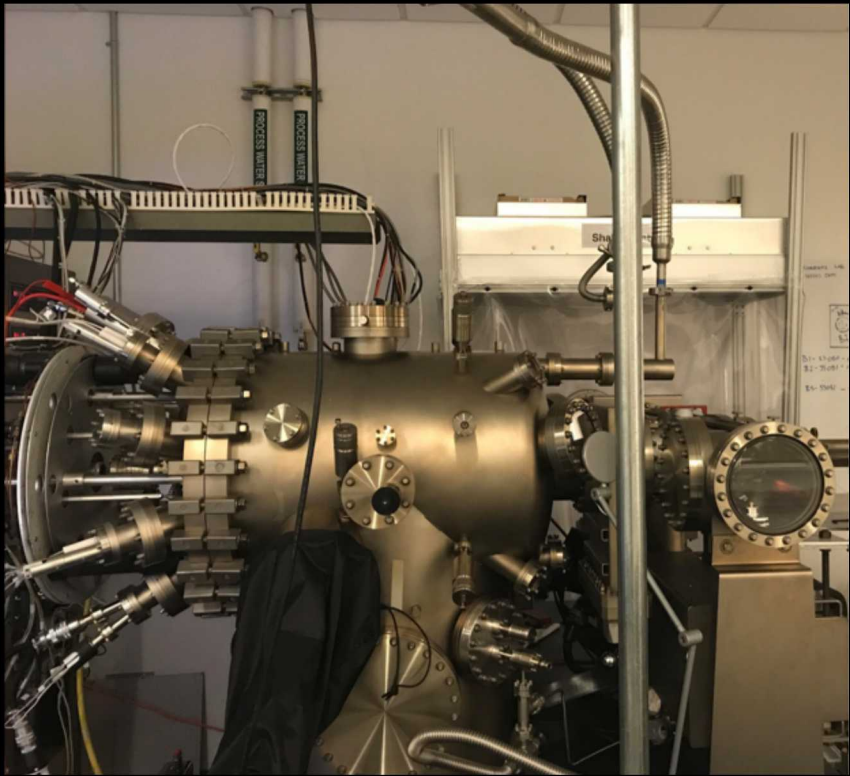
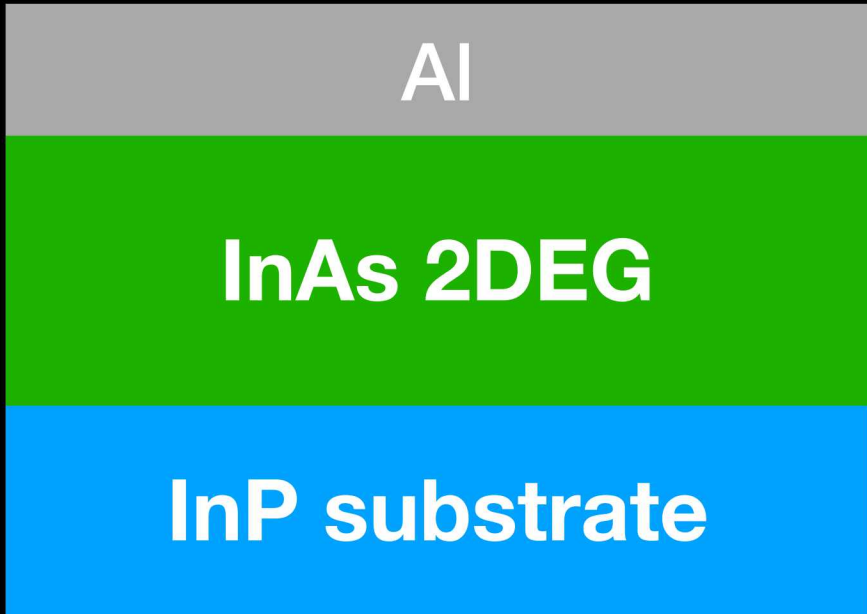
Conduction enhancement

No scattering at the S-N interface ($w=0$)
 +
 Perfectly matching fermi velocity
 =
 2x conduction enhancement

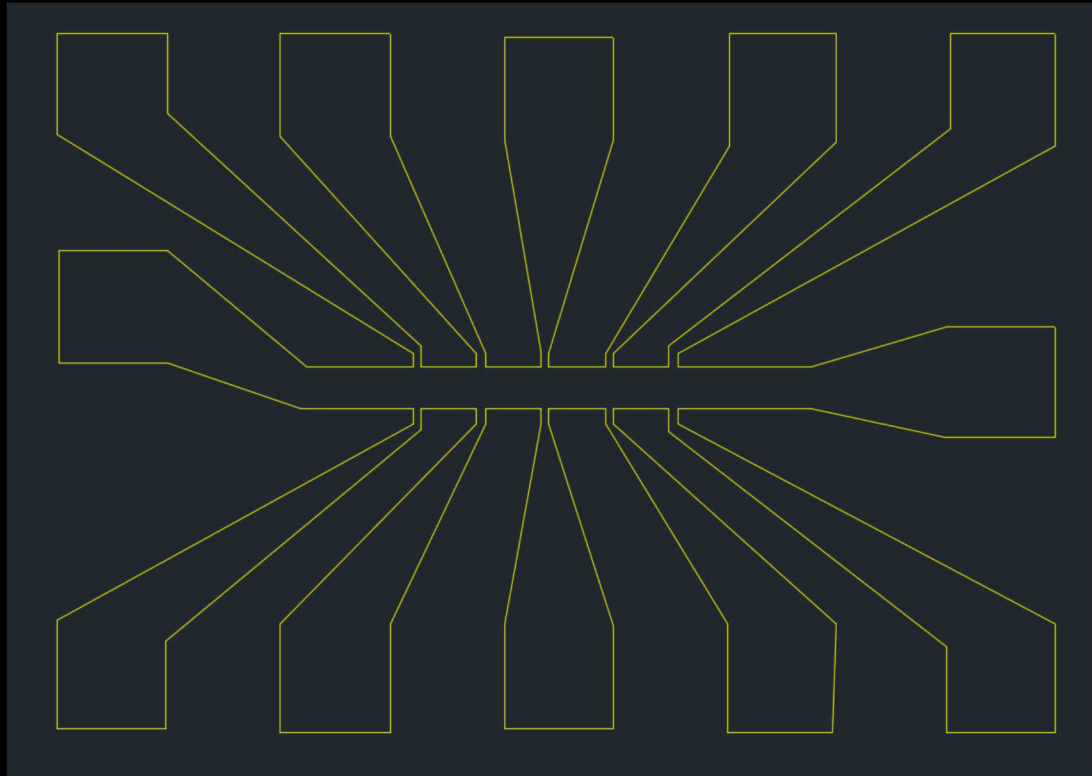
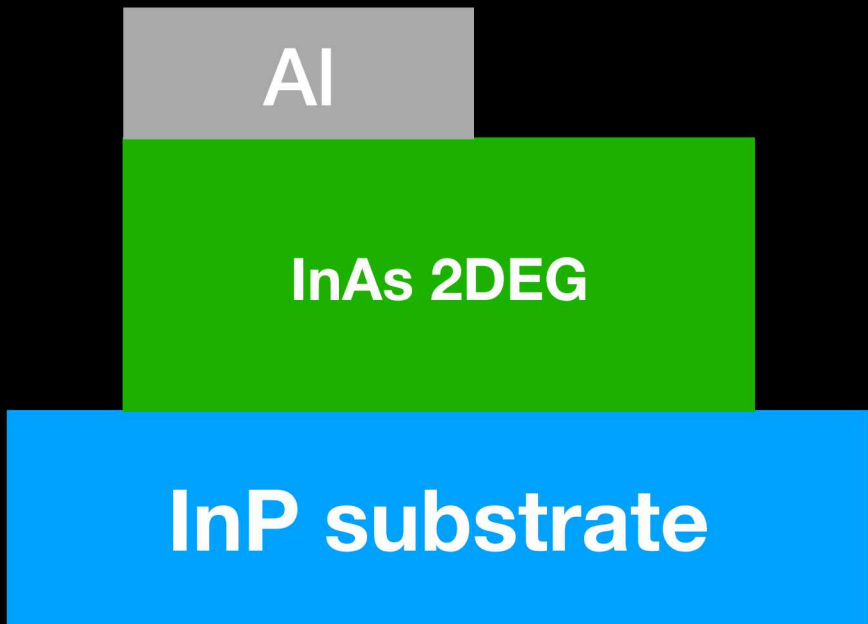




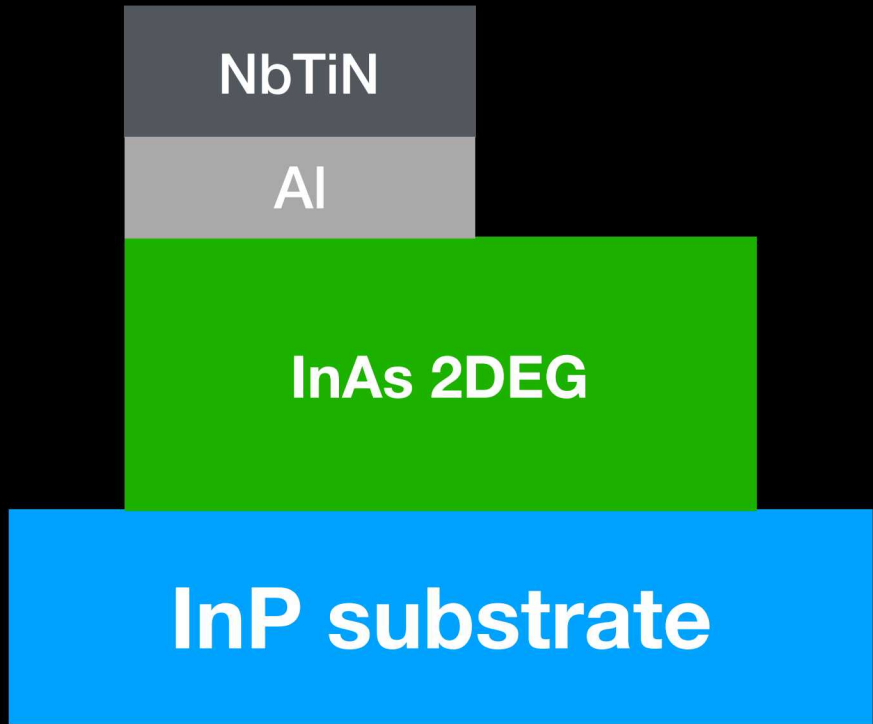
MBE grown sample



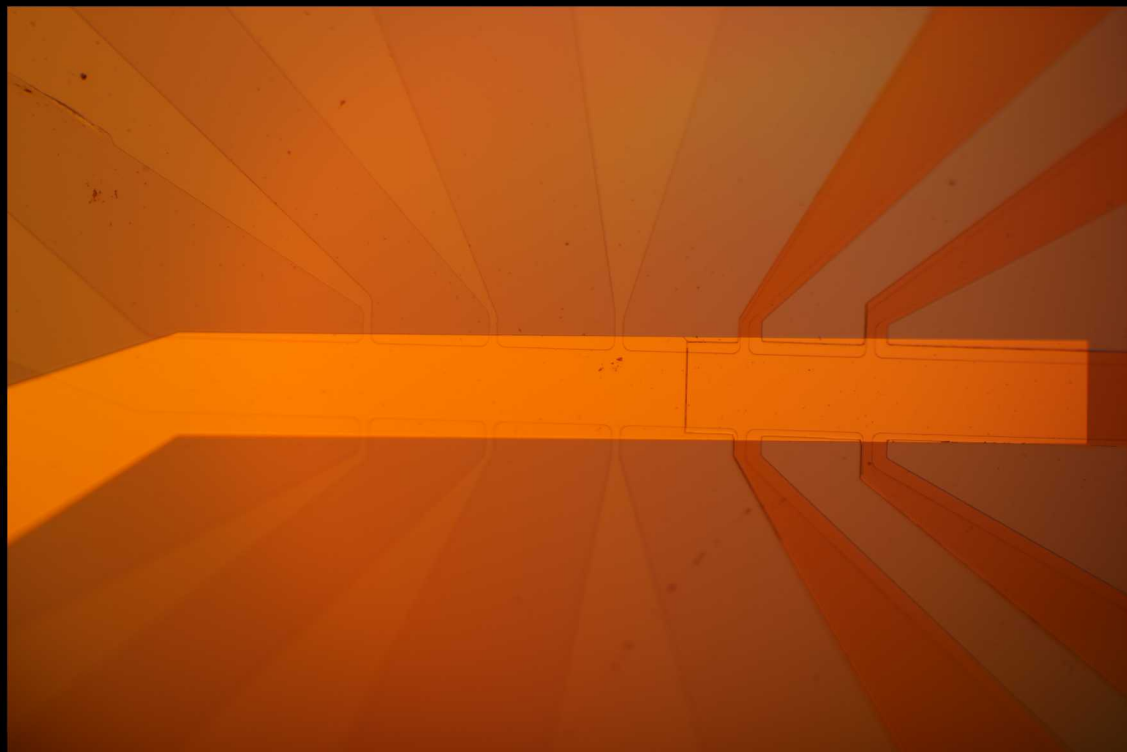
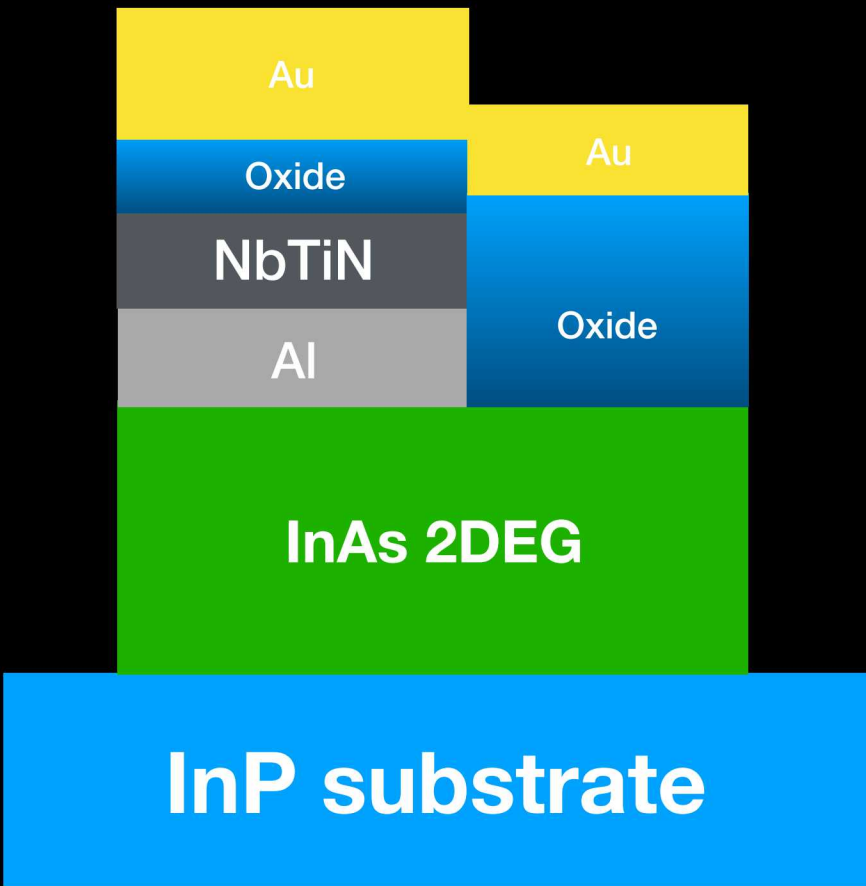
Hall-bar



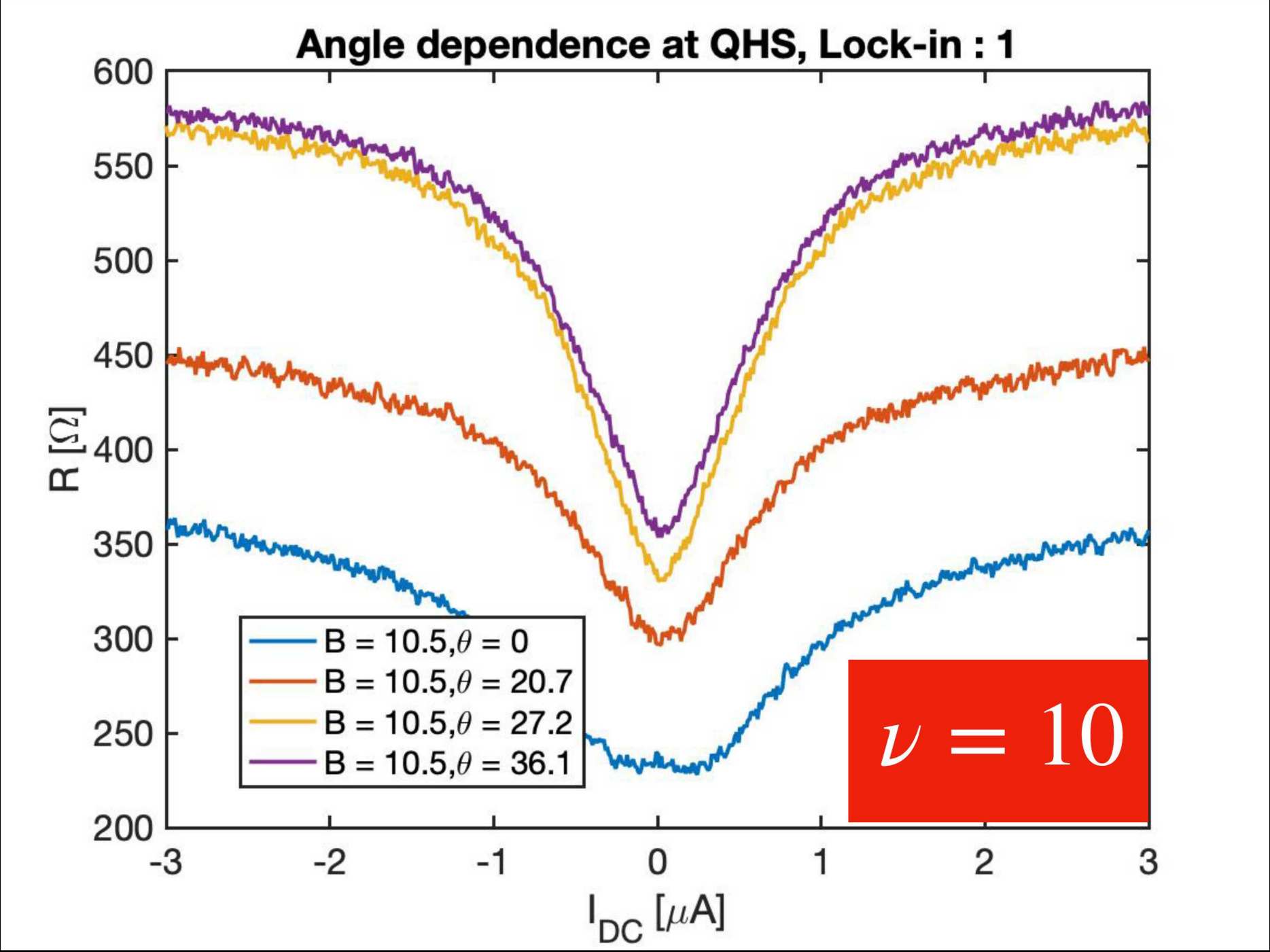
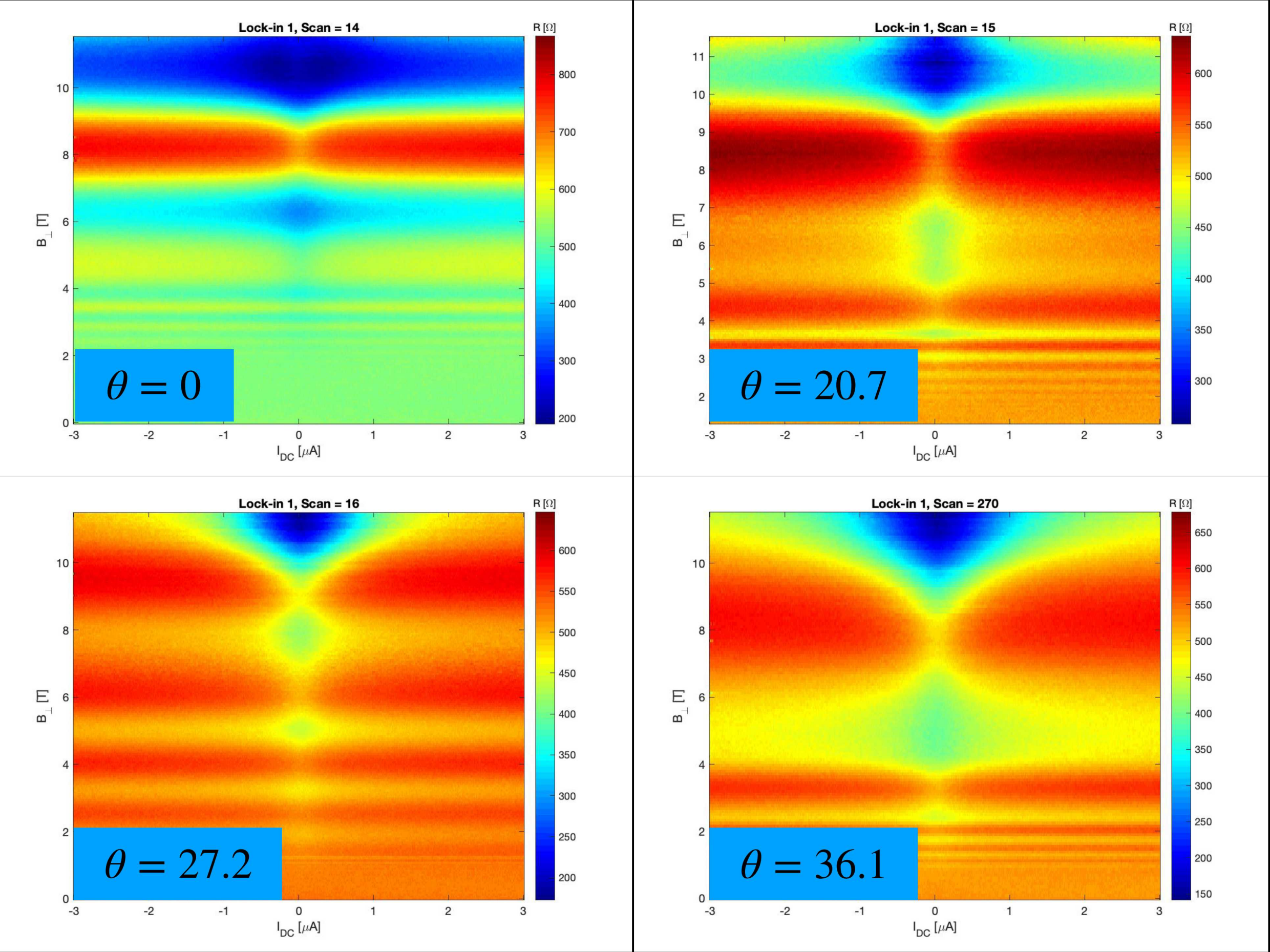
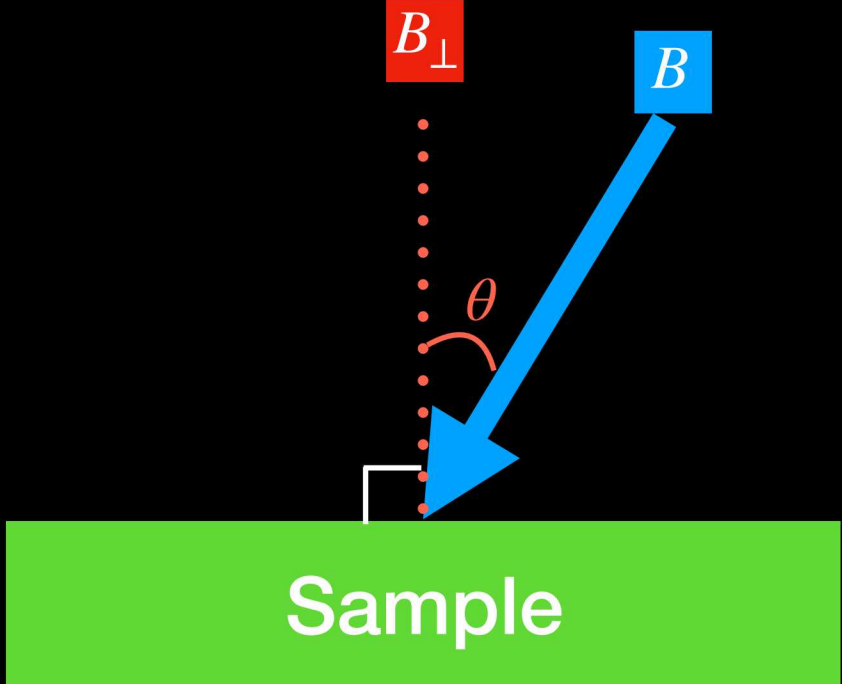
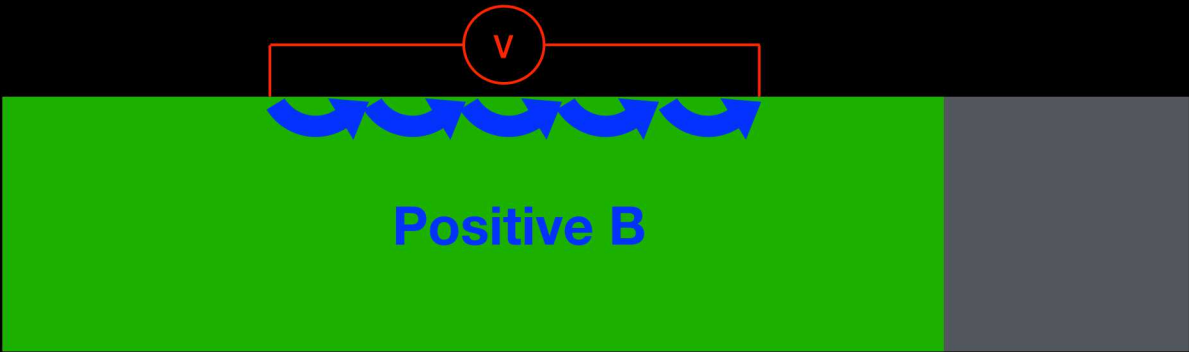
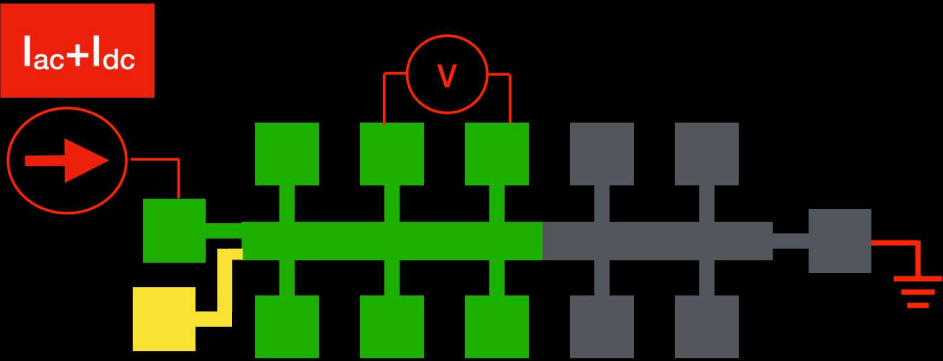
NbTiN deposition



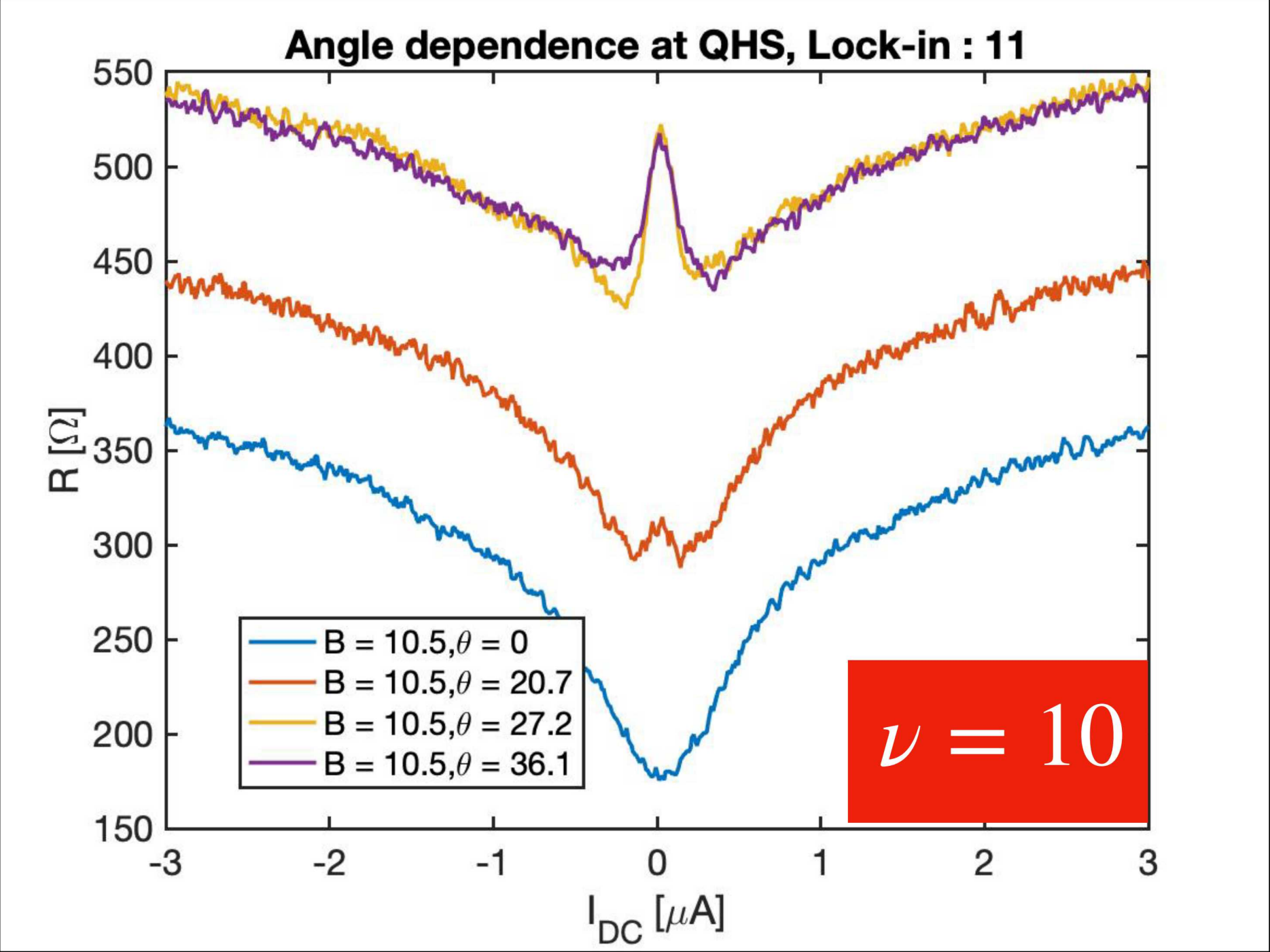
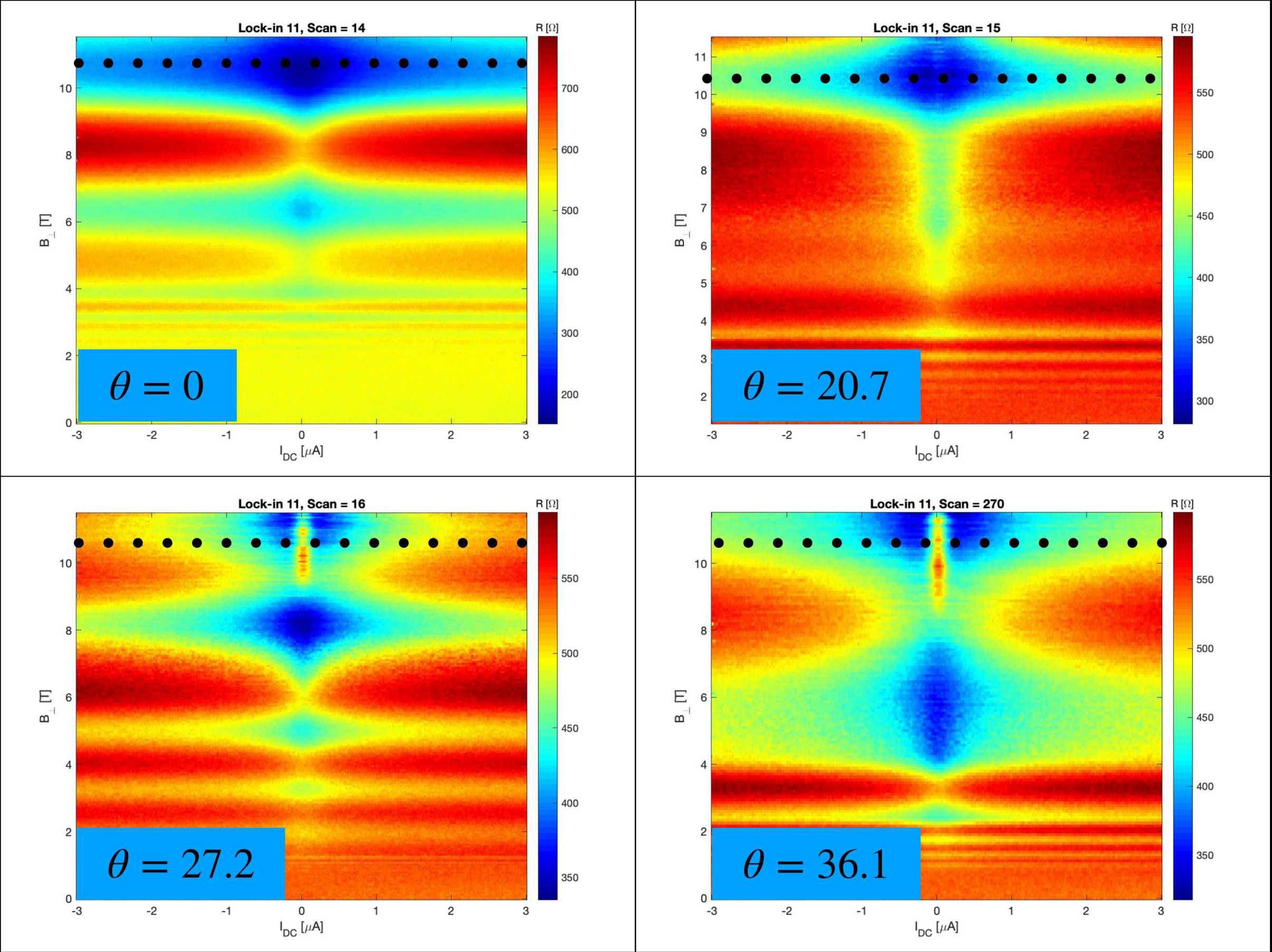
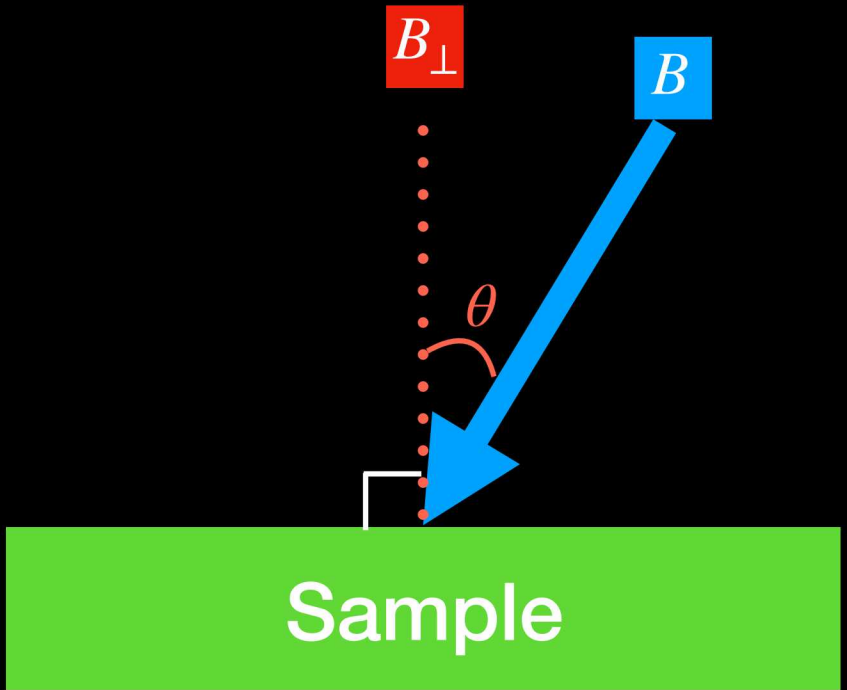
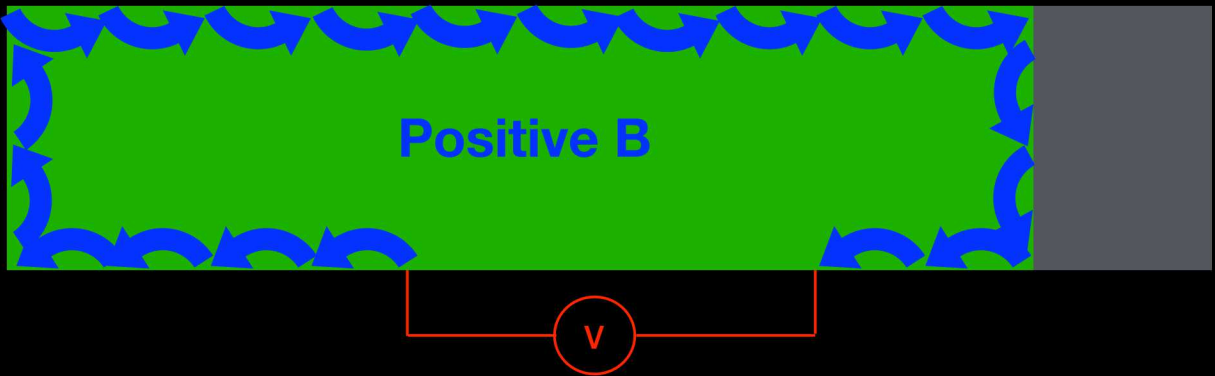
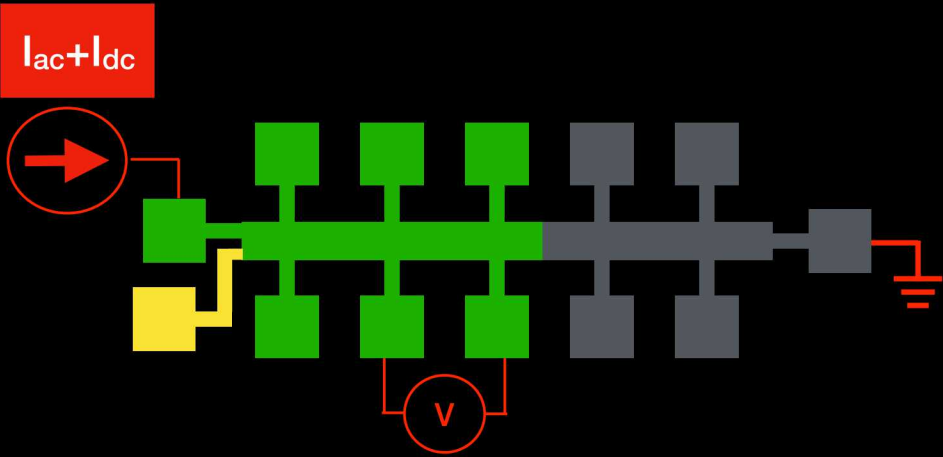
Gate



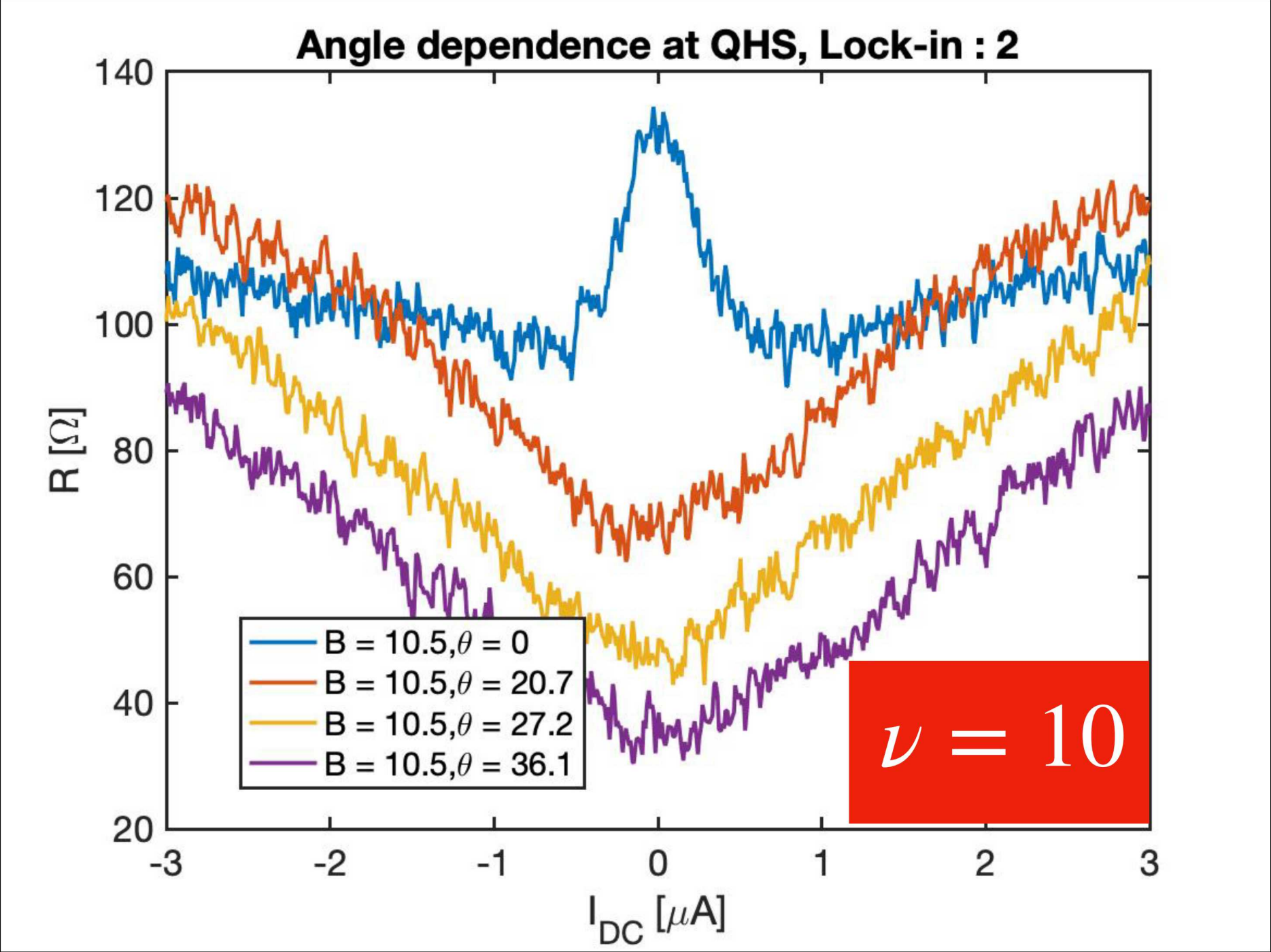
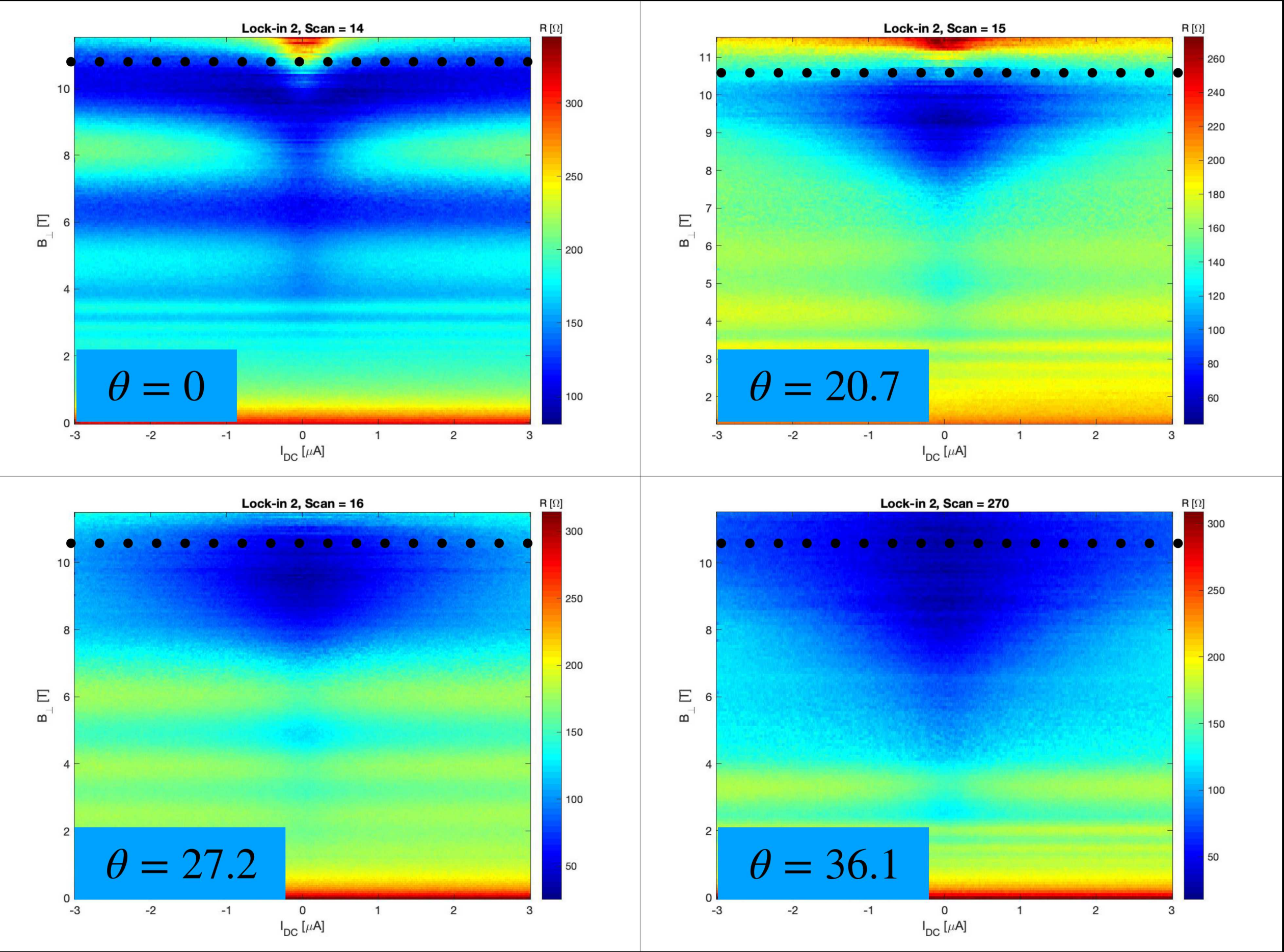
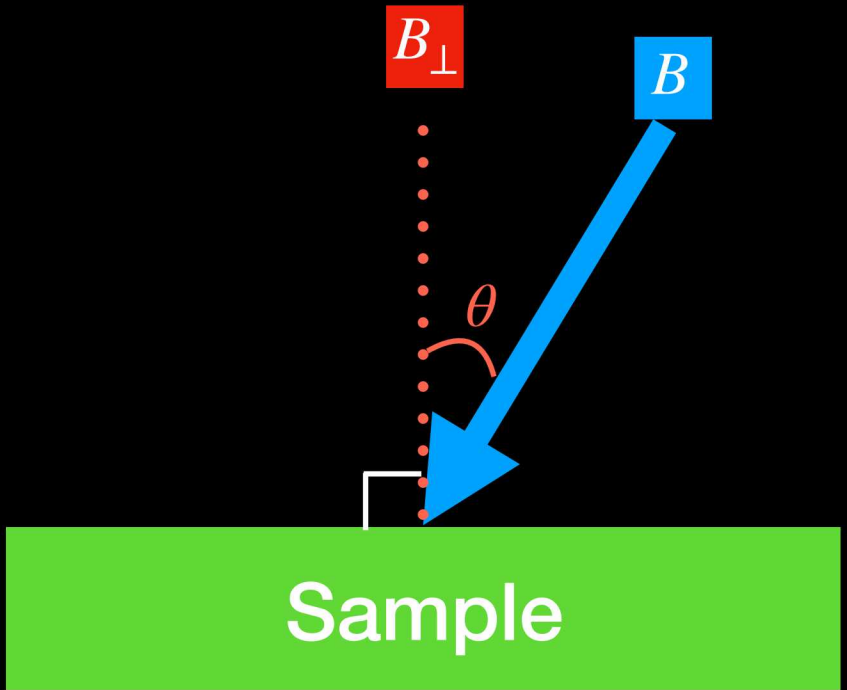
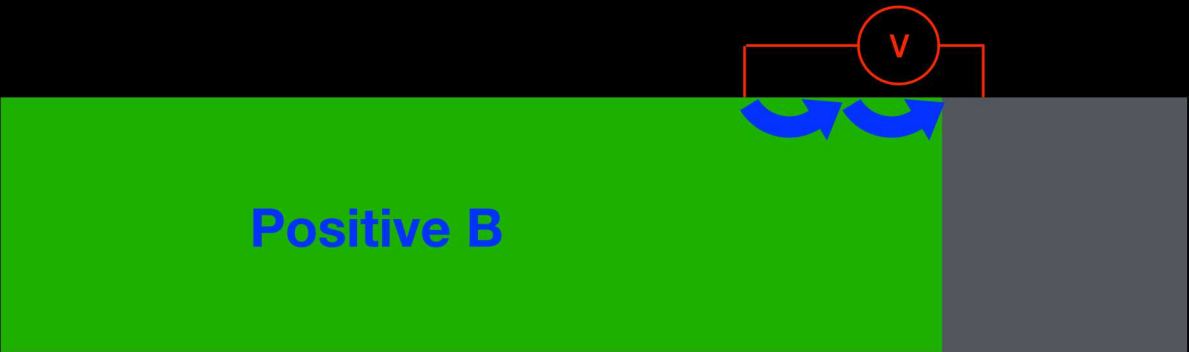
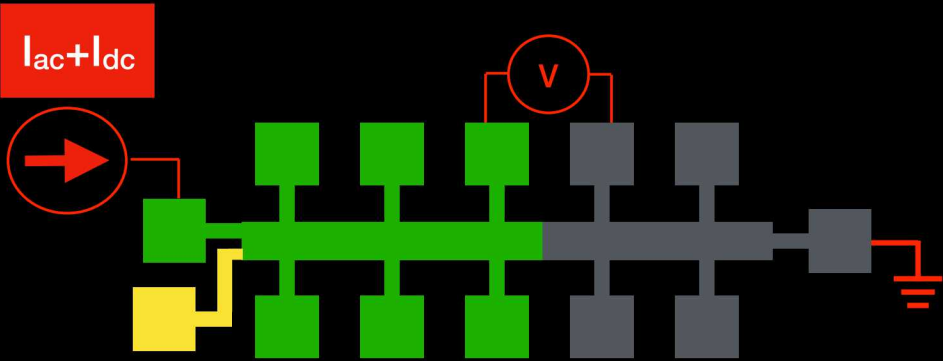
Angle Dependence



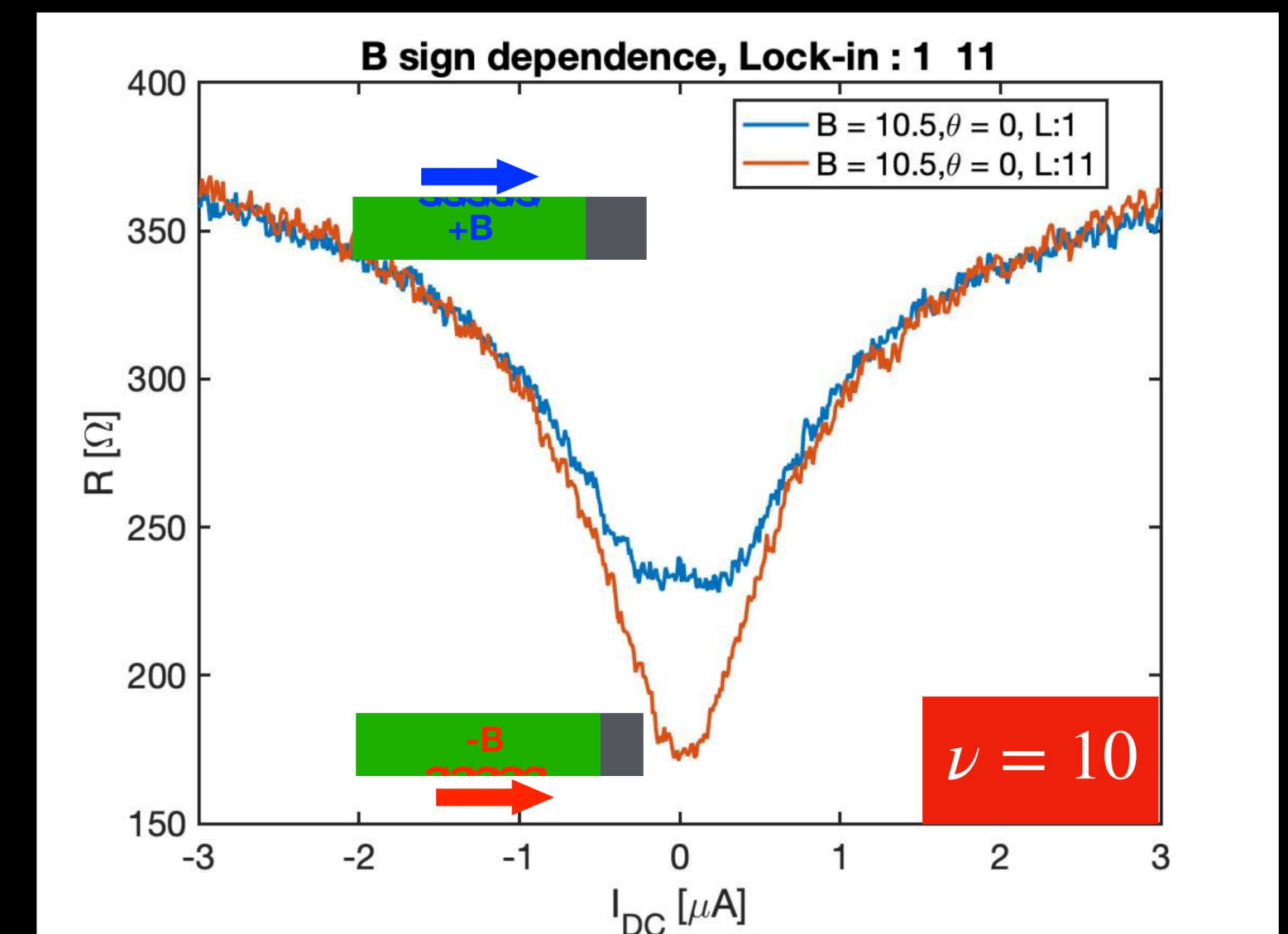
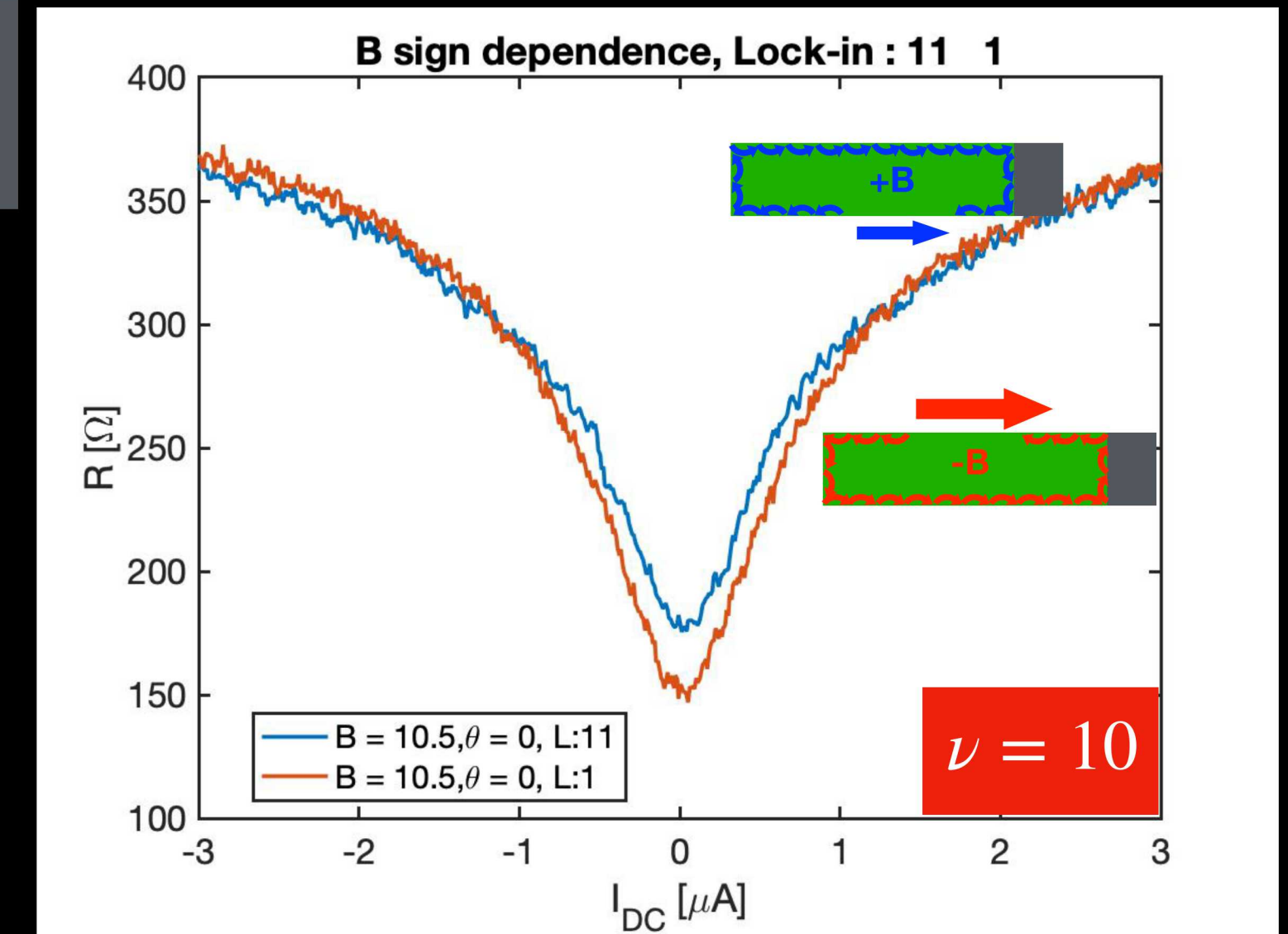
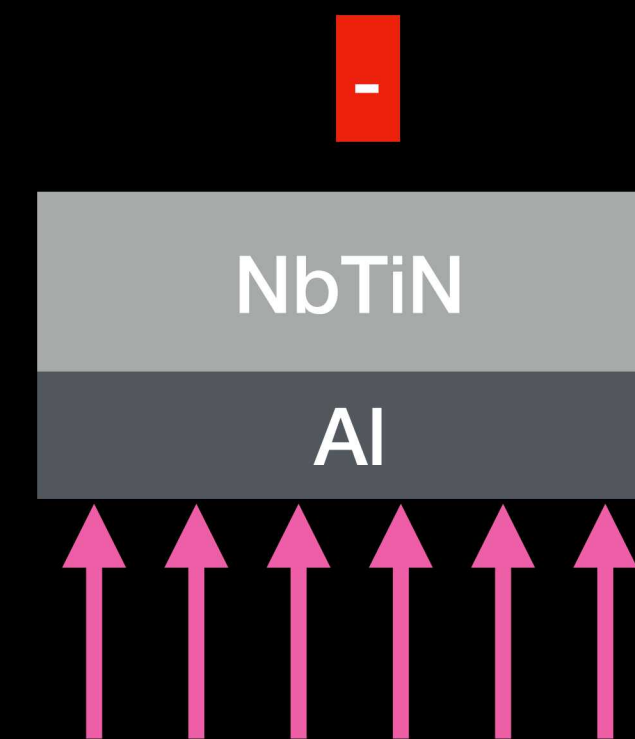
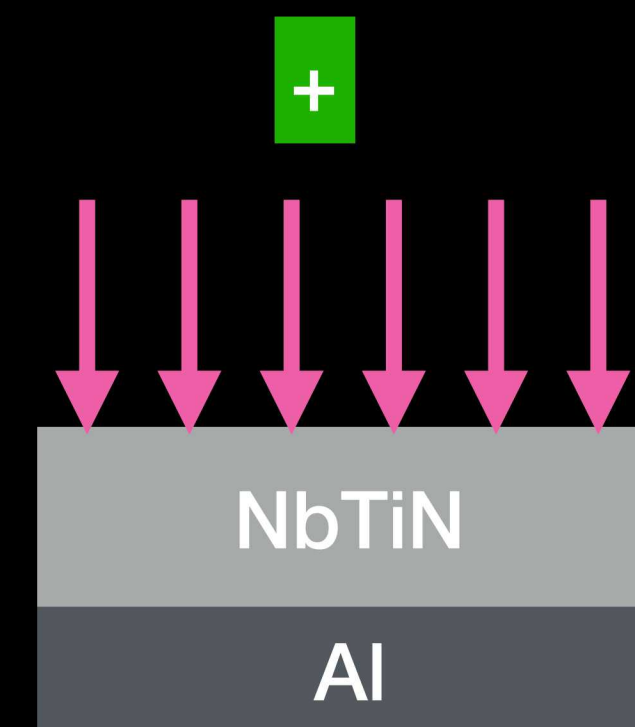
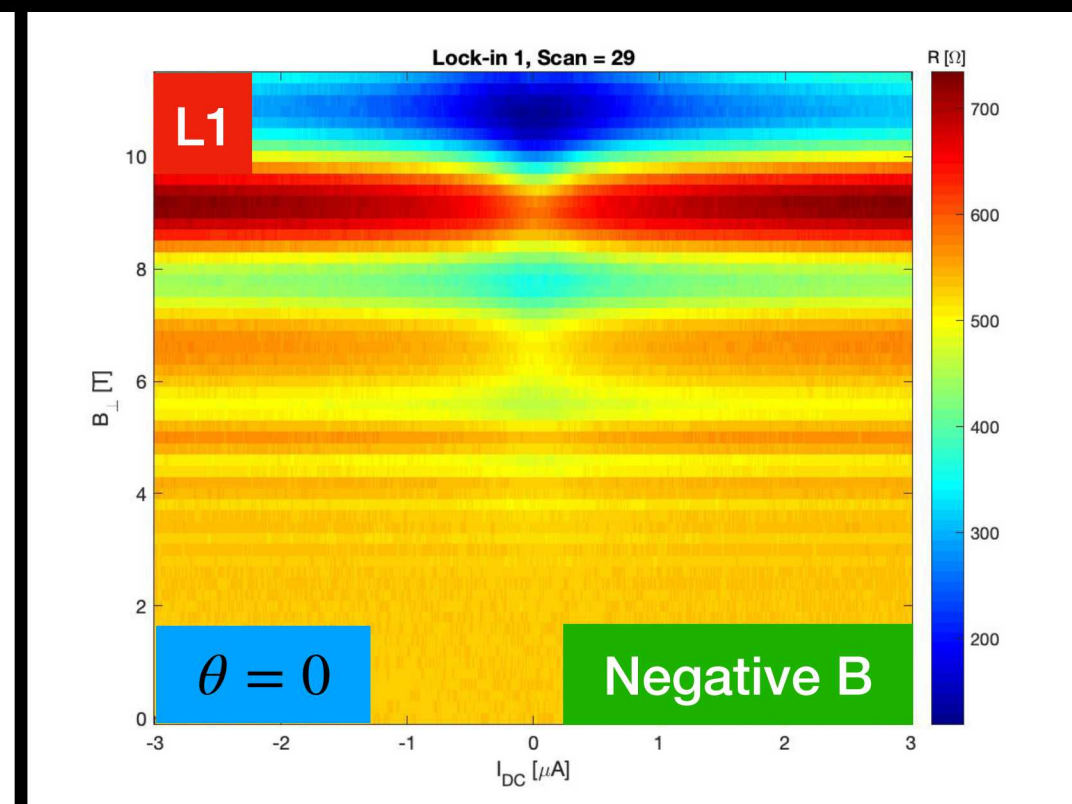
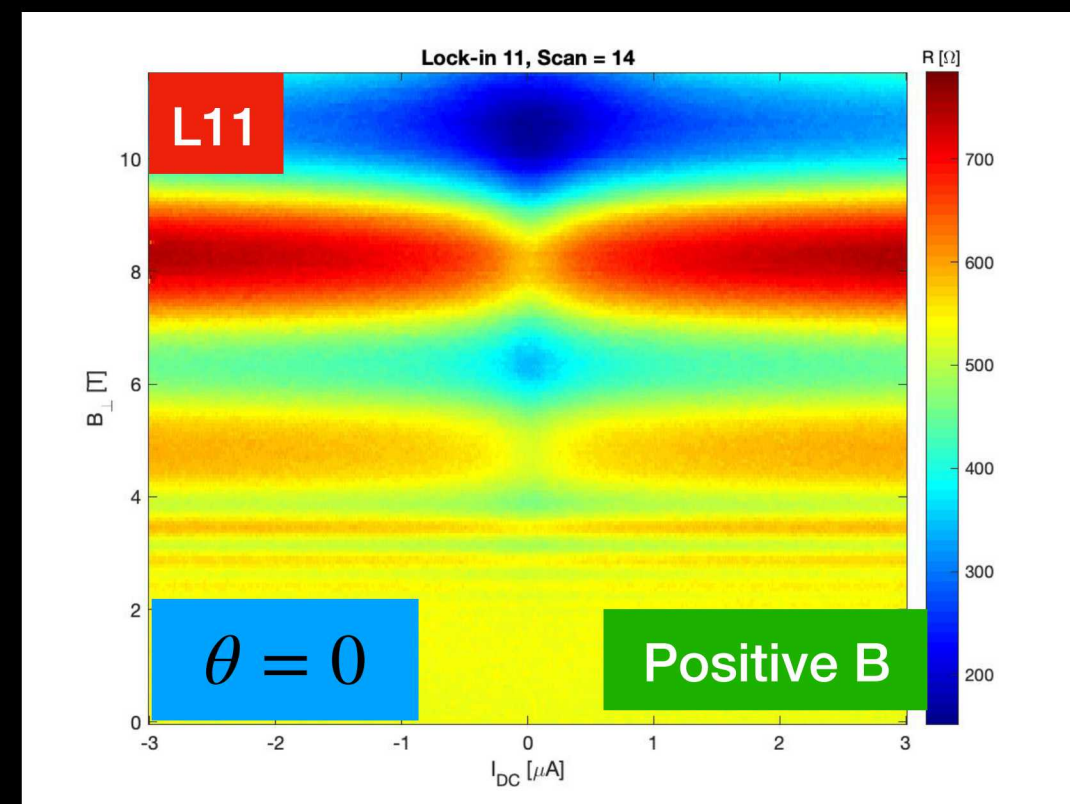
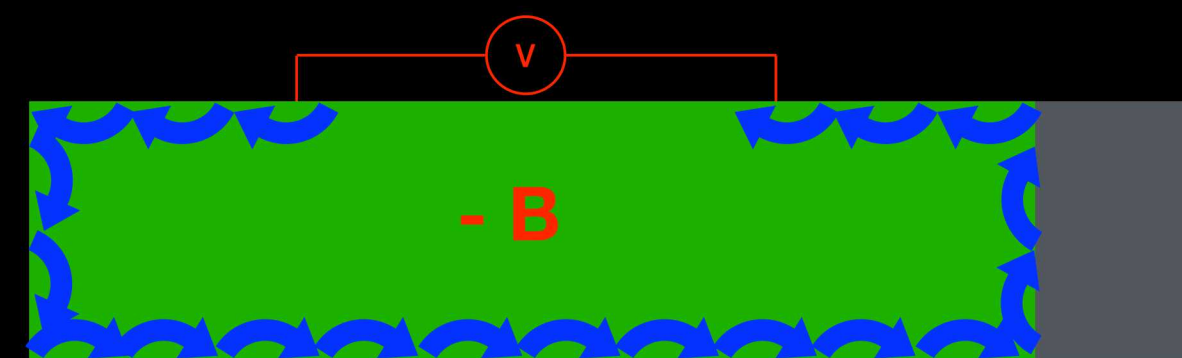
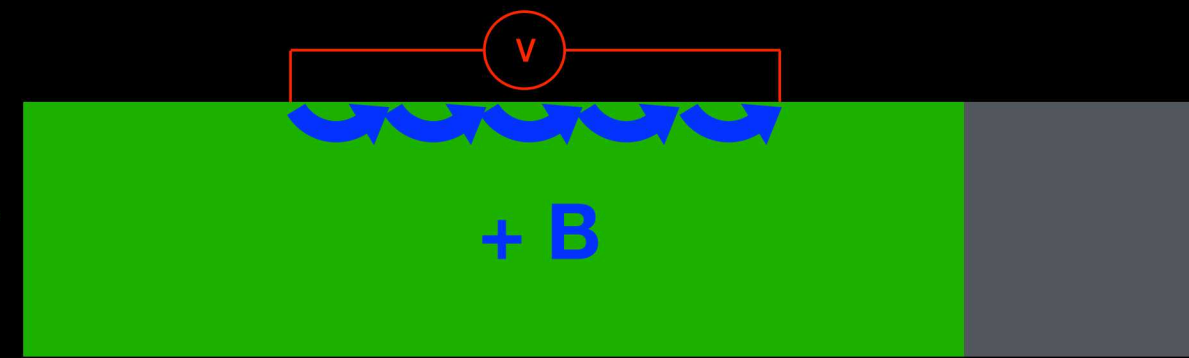
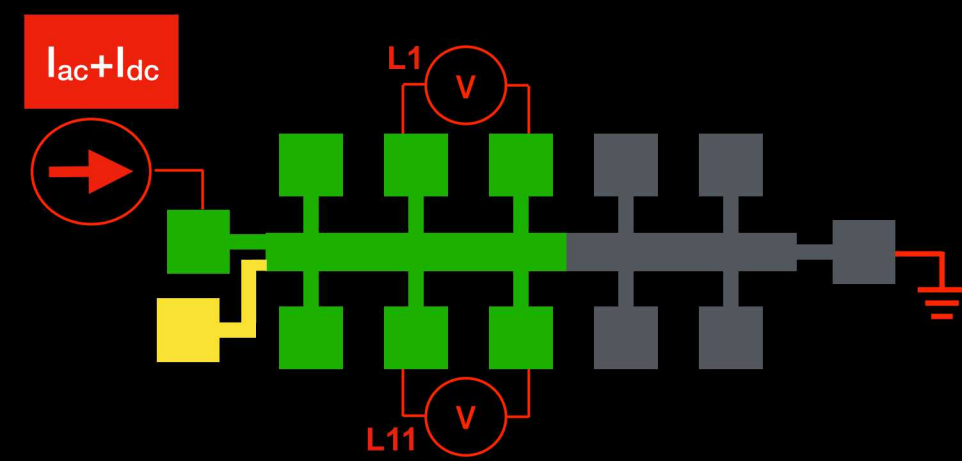
Angle Dependence



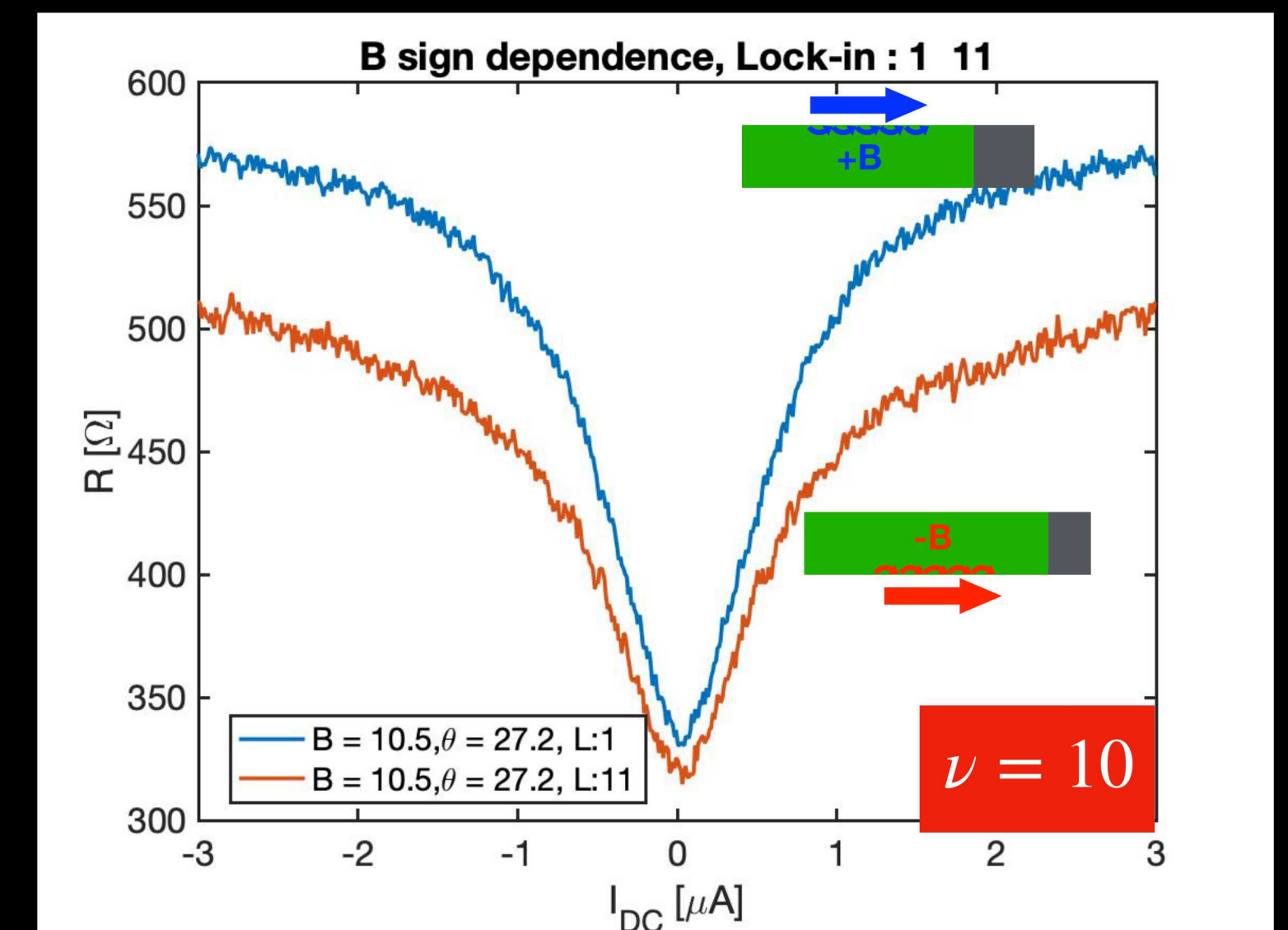
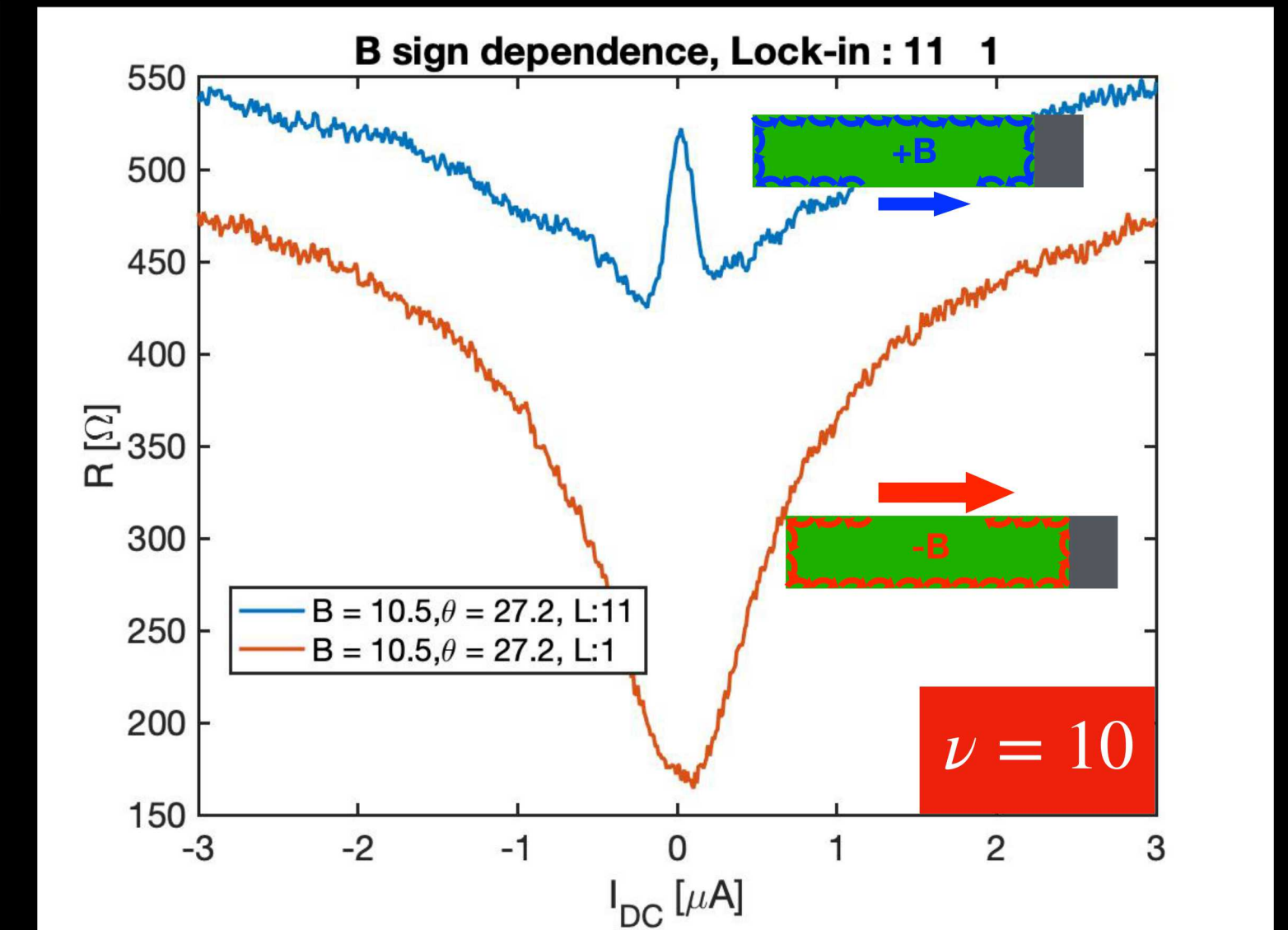
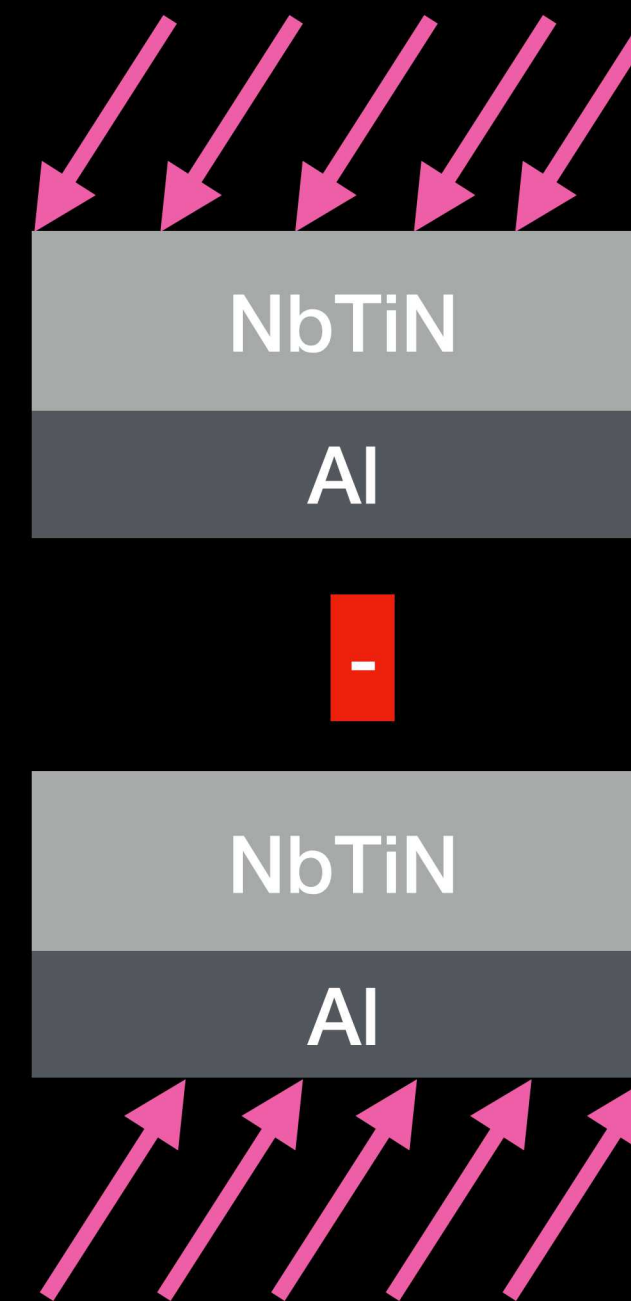
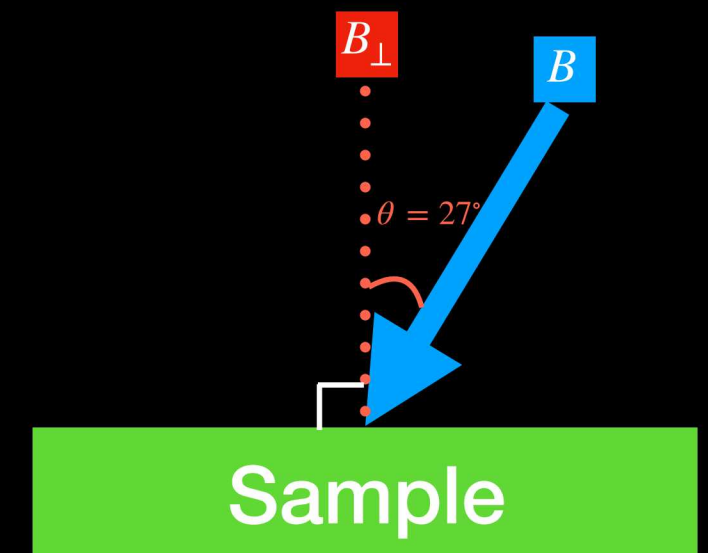
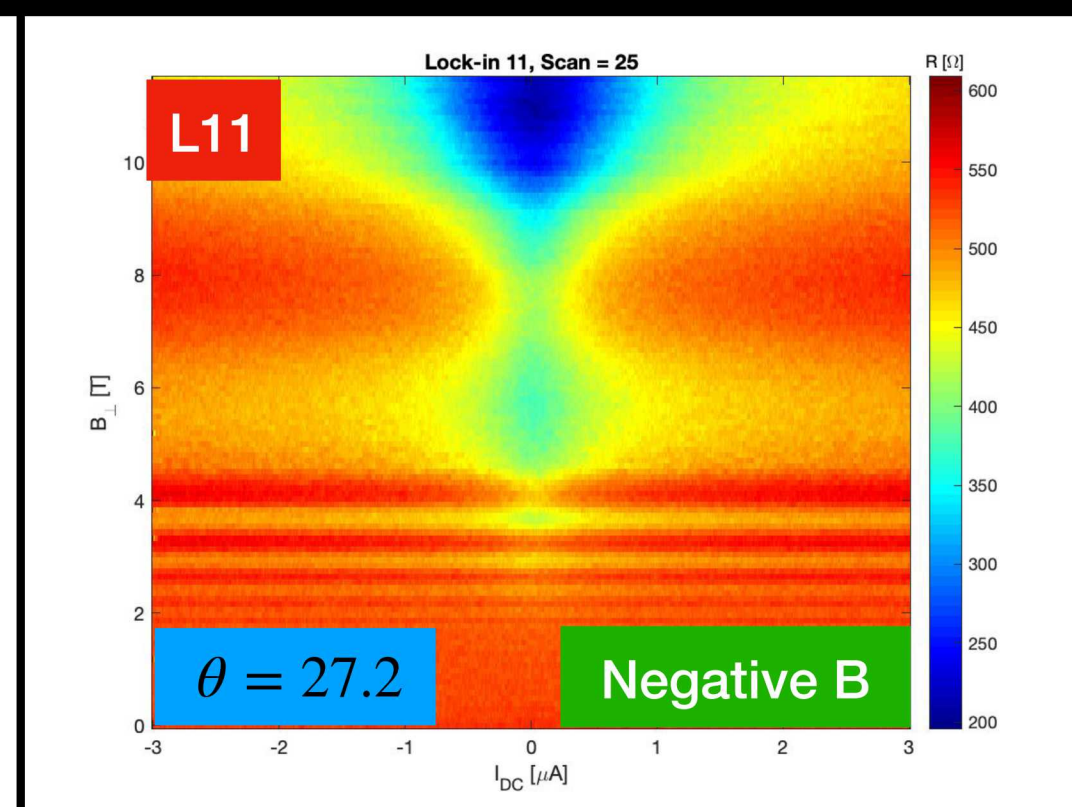
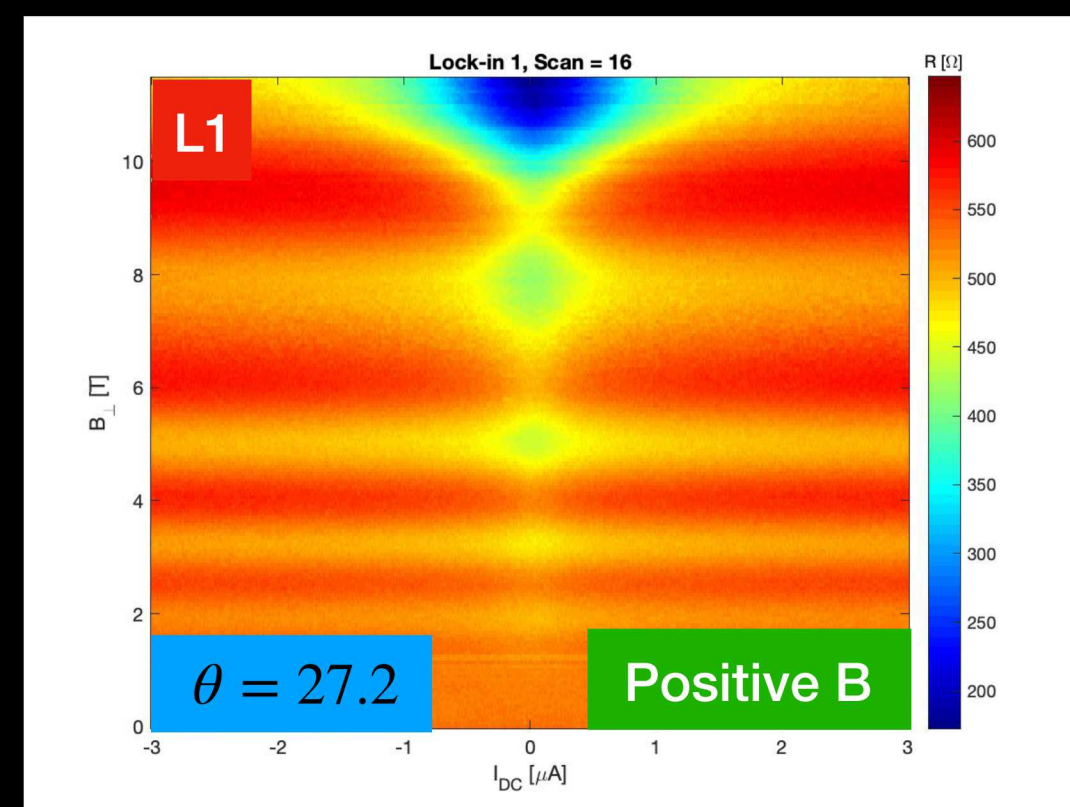
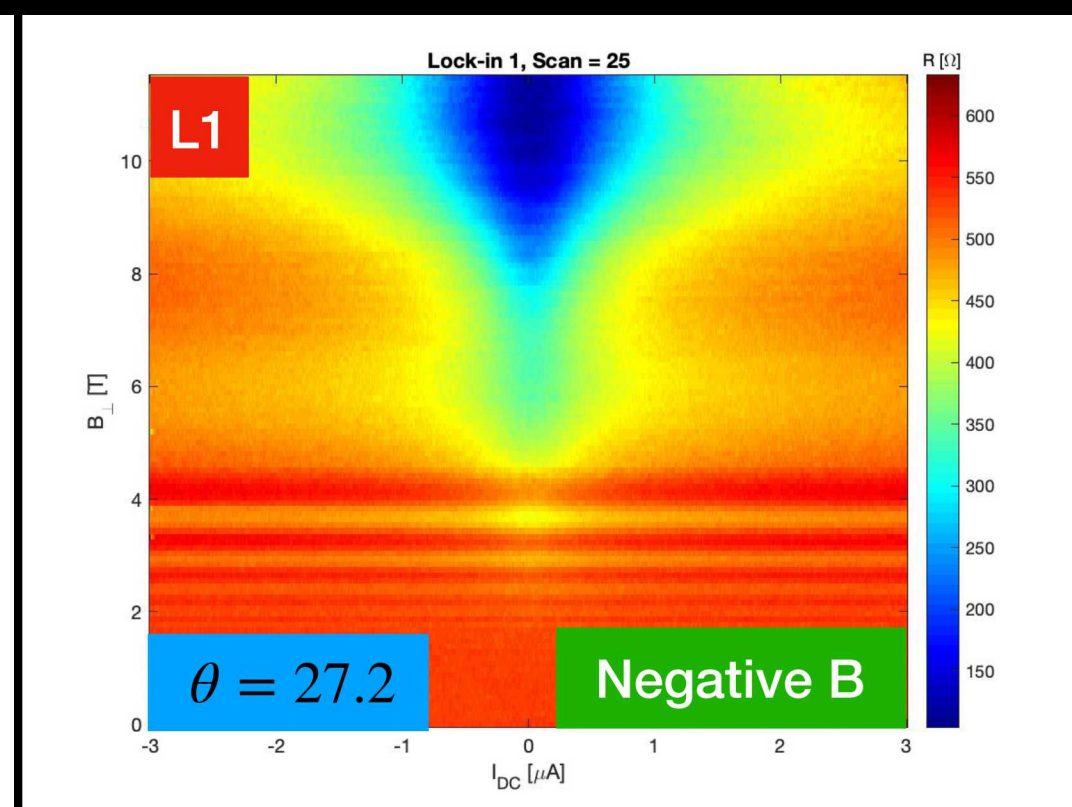
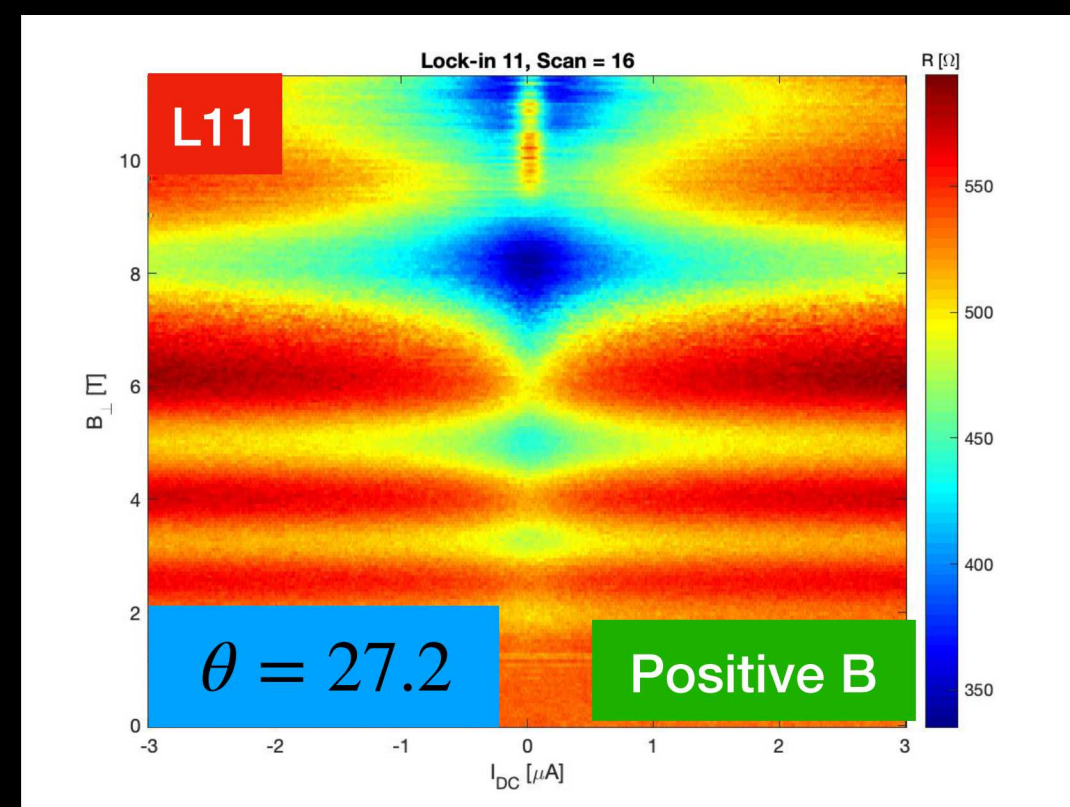
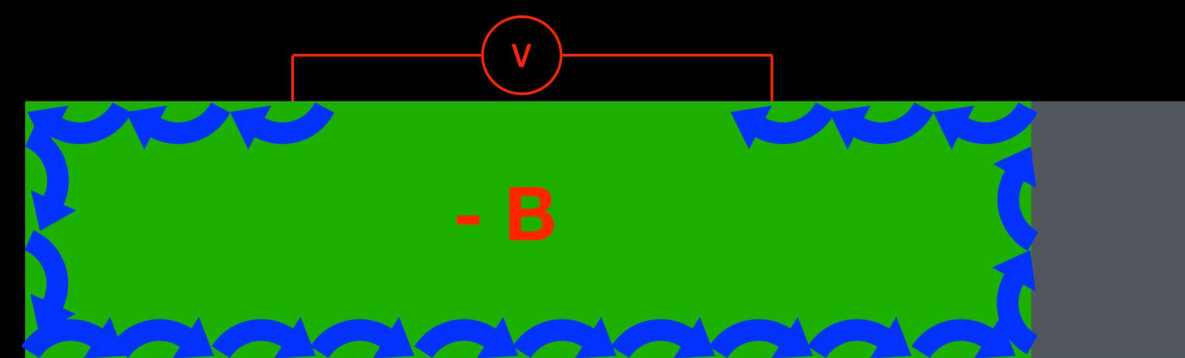
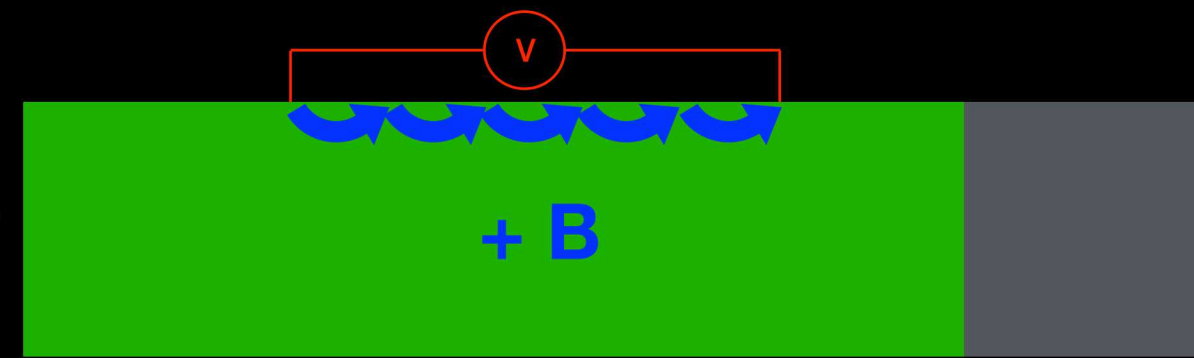
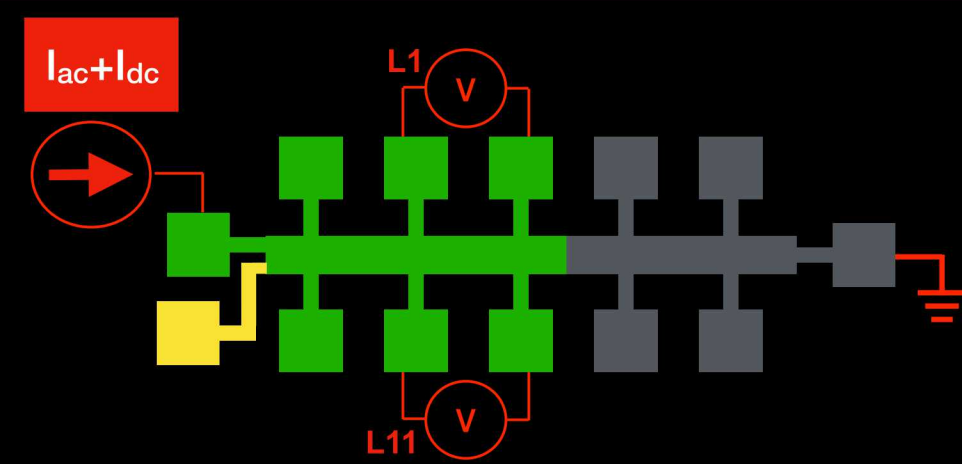
Angle Dependence



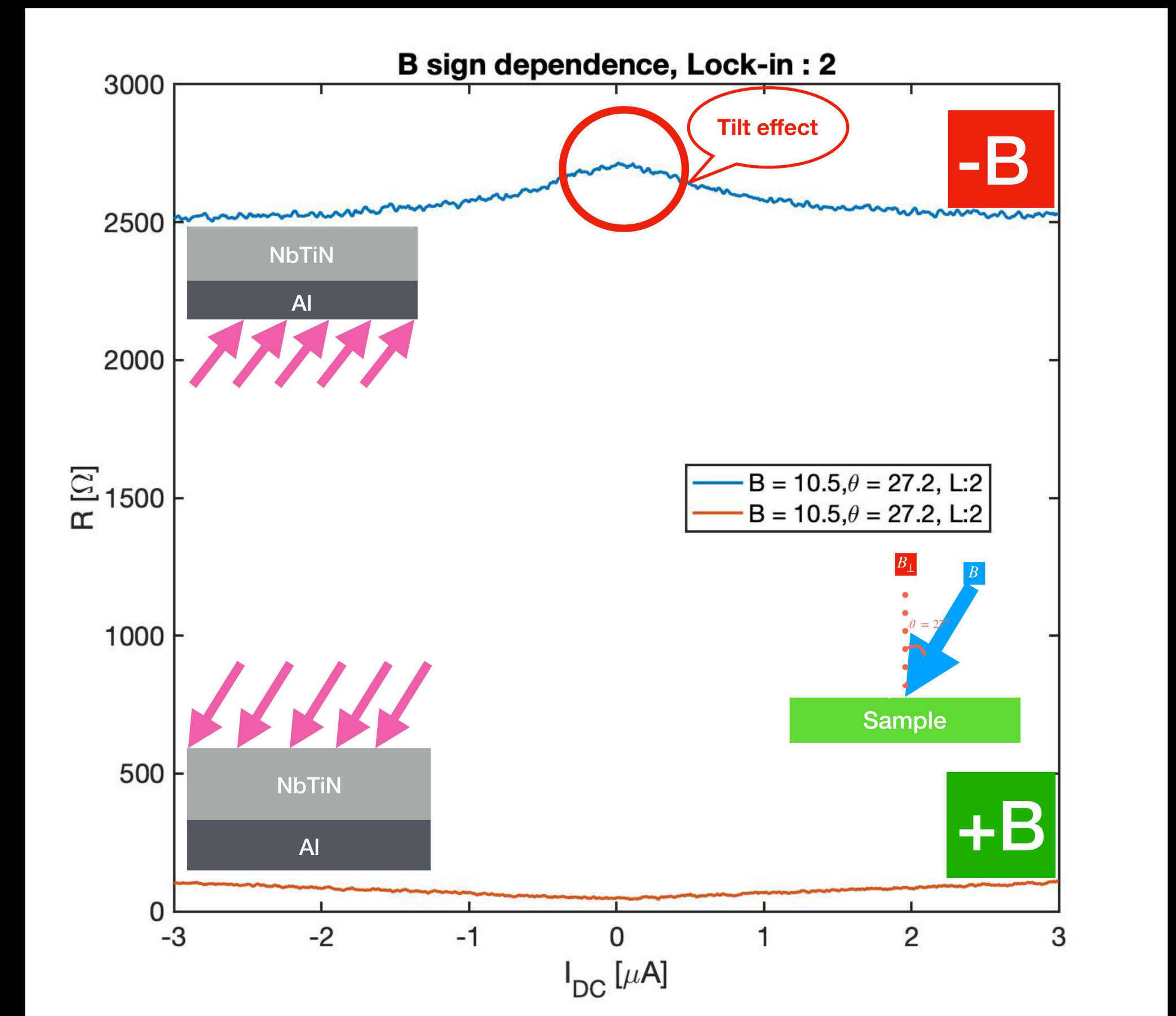
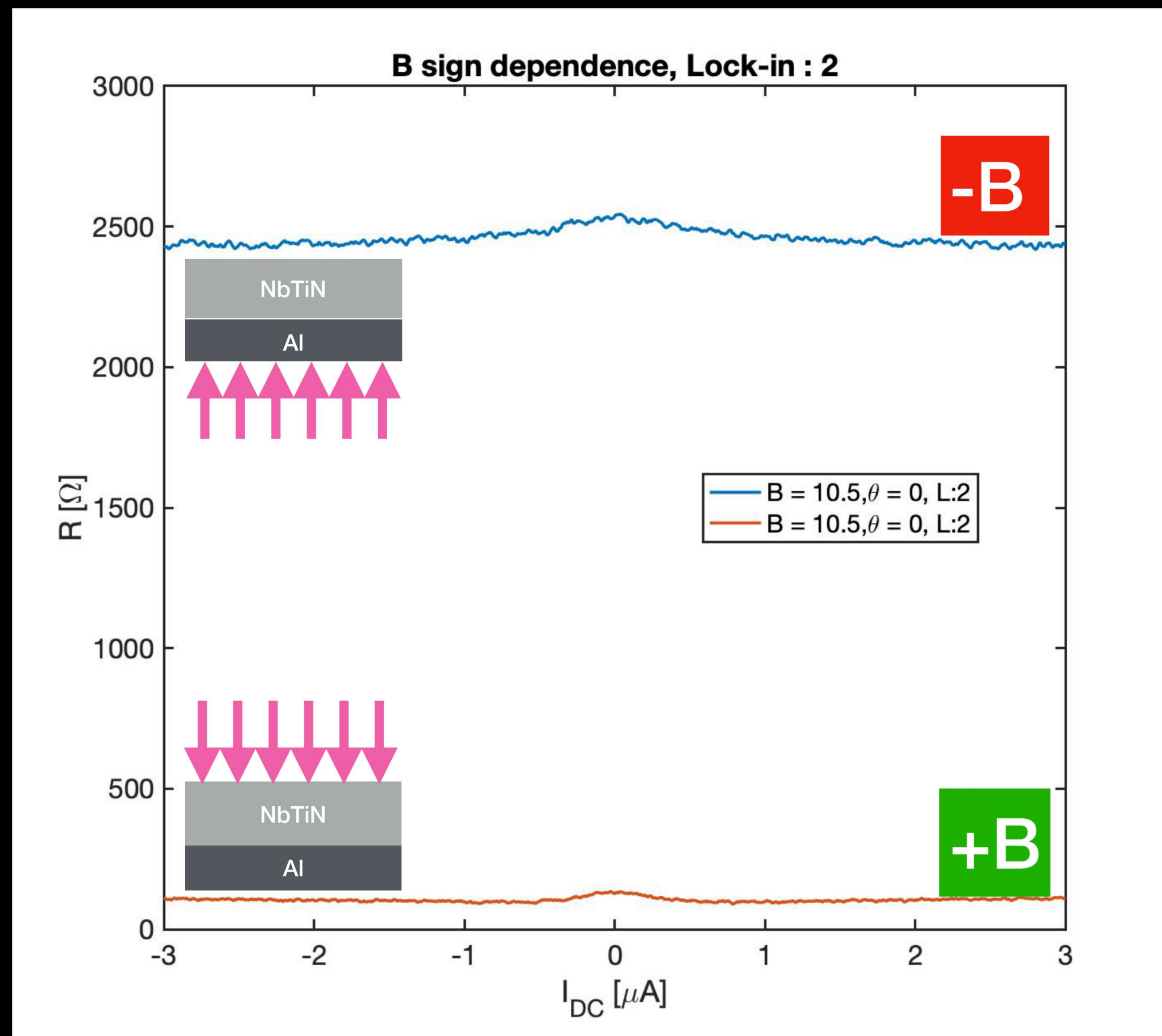
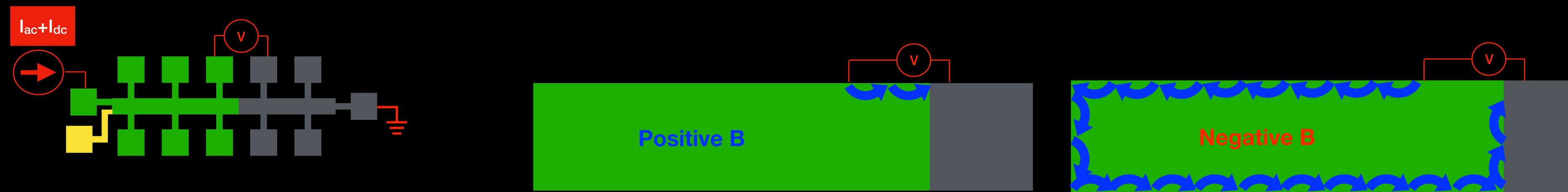
B Sign Dependence

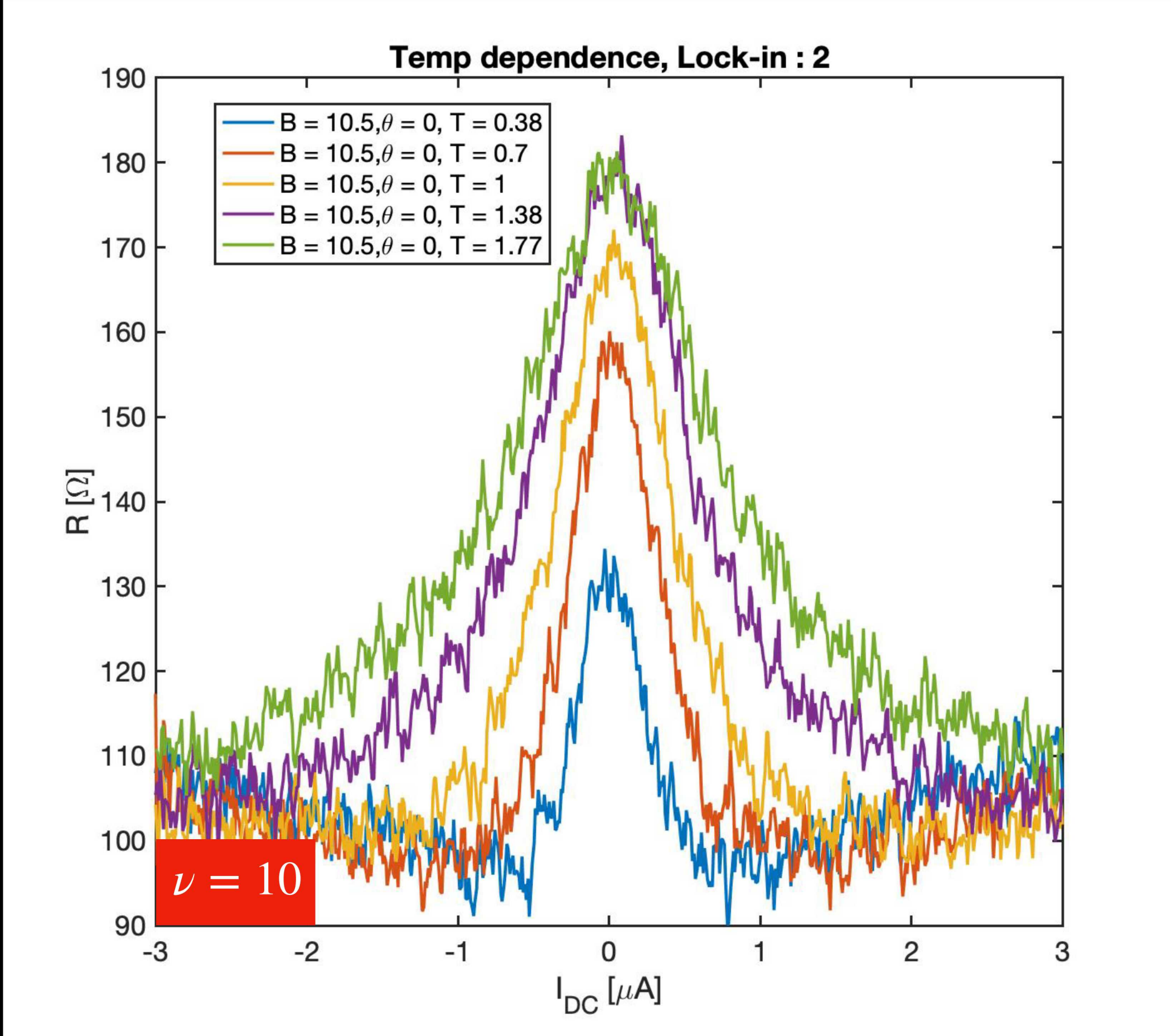
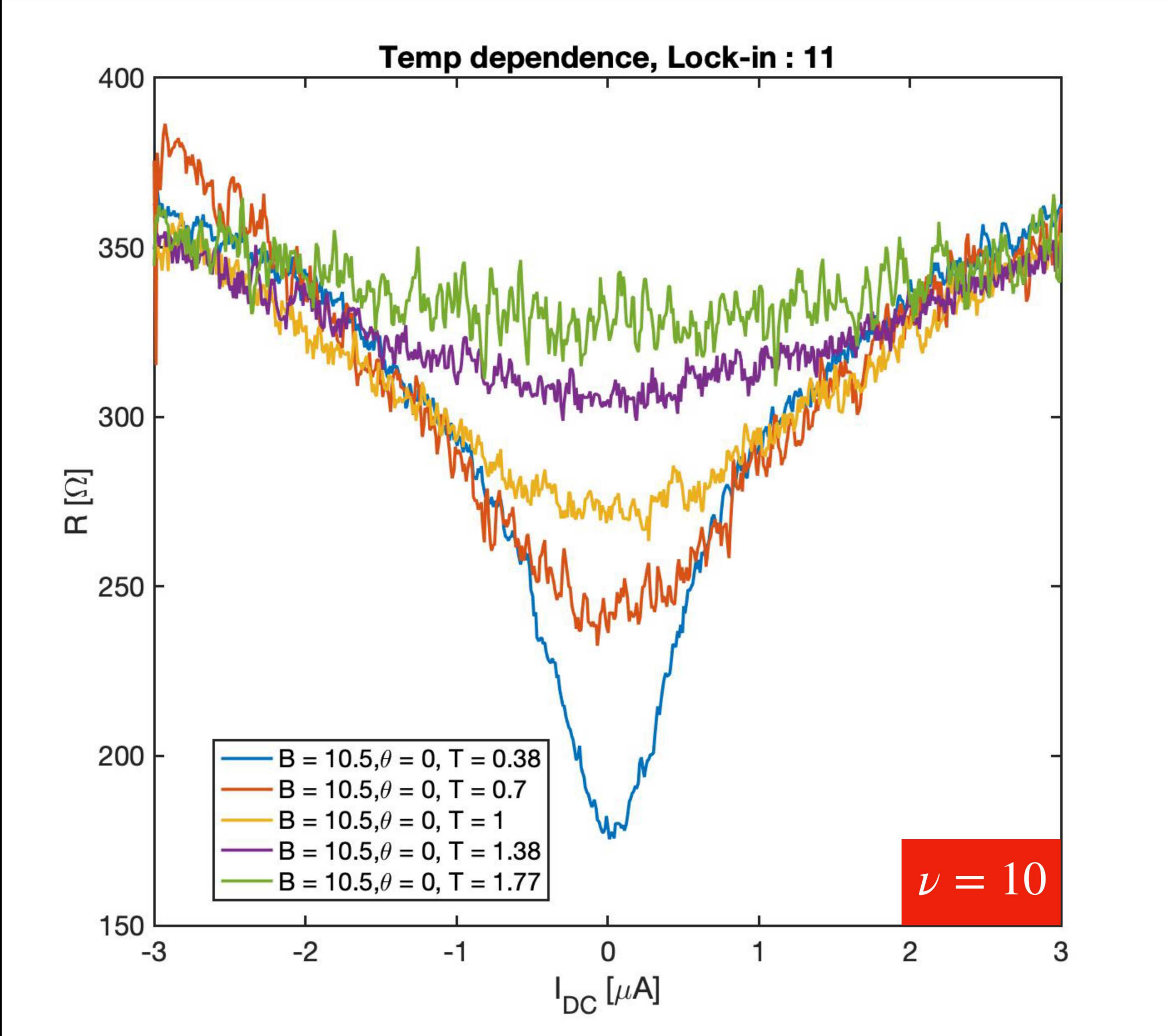
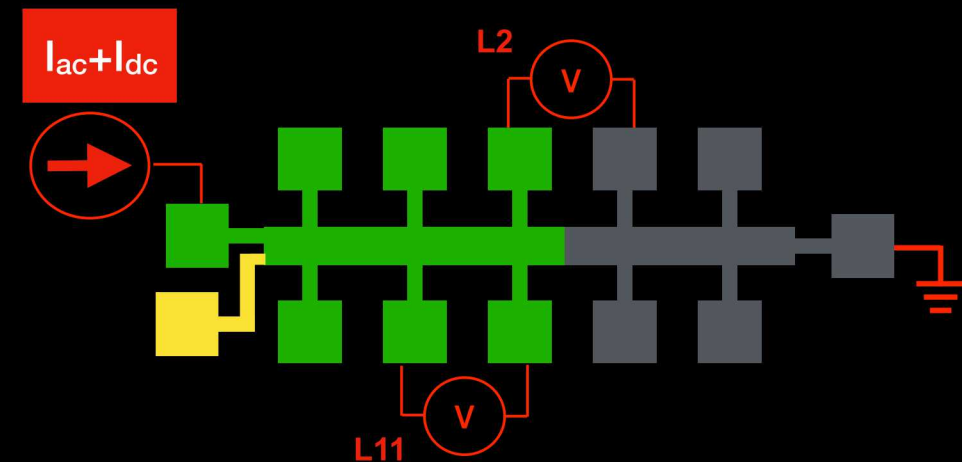


B Sign Dependence



B Sign Dependence





- Continue with better 2DEGs
- Epitaxial NbTi on Al and try subtraction device fabrication
- Add gating to the structure for in-situ changes in density and quantum Hall states



This work was performed, in part, at the Center for Integrated Nanotechnologies, a U.S. DOE, Office of Basic Energy Sciences, user facility. Sandia National Laboratories is a multimission laboratory managed and operated by National Technology and Engineering Solutions of Sandia LLC, a wholly owned subsidiary of Honeywell International Inc. for the U.S. Department of Energy's National Nuclear Security Administration under contract DE-NA0003525. The views expressed in the article do not necessarily represent the views of the U.S. Department of Energy or the United States Government.